



US006853142B2

(12) **United States Patent**
Chistyakov

(10) **Patent No.:** **US 6,853,142 B2**
(45) **Date of Patent:** **Feb. 8, 2005**

(54) **METHODS AND APPARATUS FOR
GENERATING HIGH-DENSITY PLASMA**

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(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 0 days.

(21) Appl. No.: **10/065,629**

(22) Filed: **Nov. 4, 2002**

(65) **Prior Publication Data**

US 2004/0085023 A1 May 6, 2004

(51) **Int. Cl.⁷** **C23C 16/452**

(52) **U.S. Cl.** **315/111.41; 156/345.33;**
118/723.1

(58) **Field of Search** 315/111.01–111.91;
156/345.21, 345.29, 345.33, 345.42, 345.44,
345; 204/298.06, 298.04, 298.08; 118/723 FE,
723.1, 723 MP; 423/210, 246, 248

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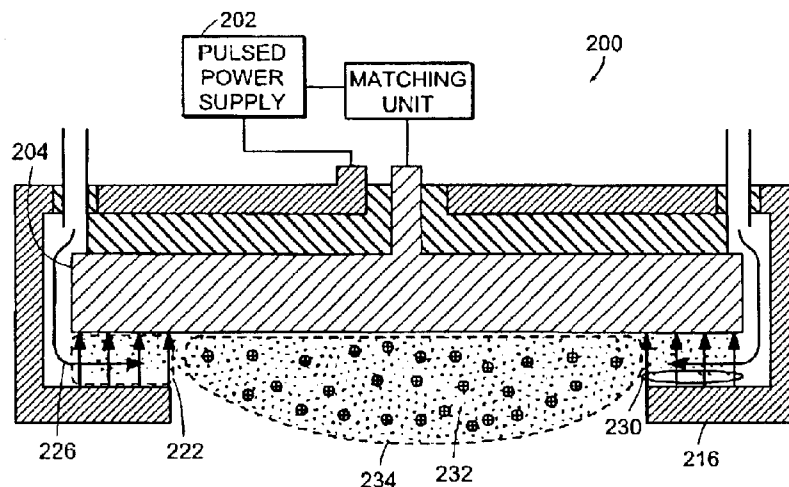
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(57) **ABSTRACT**

Methods and apparatus for generating a strongly-ionized plasma are described. An apparatus for generating a strongly-ionized plasma according to the present invention includes an anode and a cathode that is positioned adjacent to the anode to form a gap there between. An ionization source generates a weakly-ionized plasma proximate to the cathode. A power supply produces an electric field in the gap between the anode and the cathode. The electric field generates excited atoms in the weakly-ionized plasma and generates secondary electrons from the cathode. The secondary electrons ionize the excited atoms, thereby creating the strongly-ionized plasma

43 Claims, 13 Drawing Sheets



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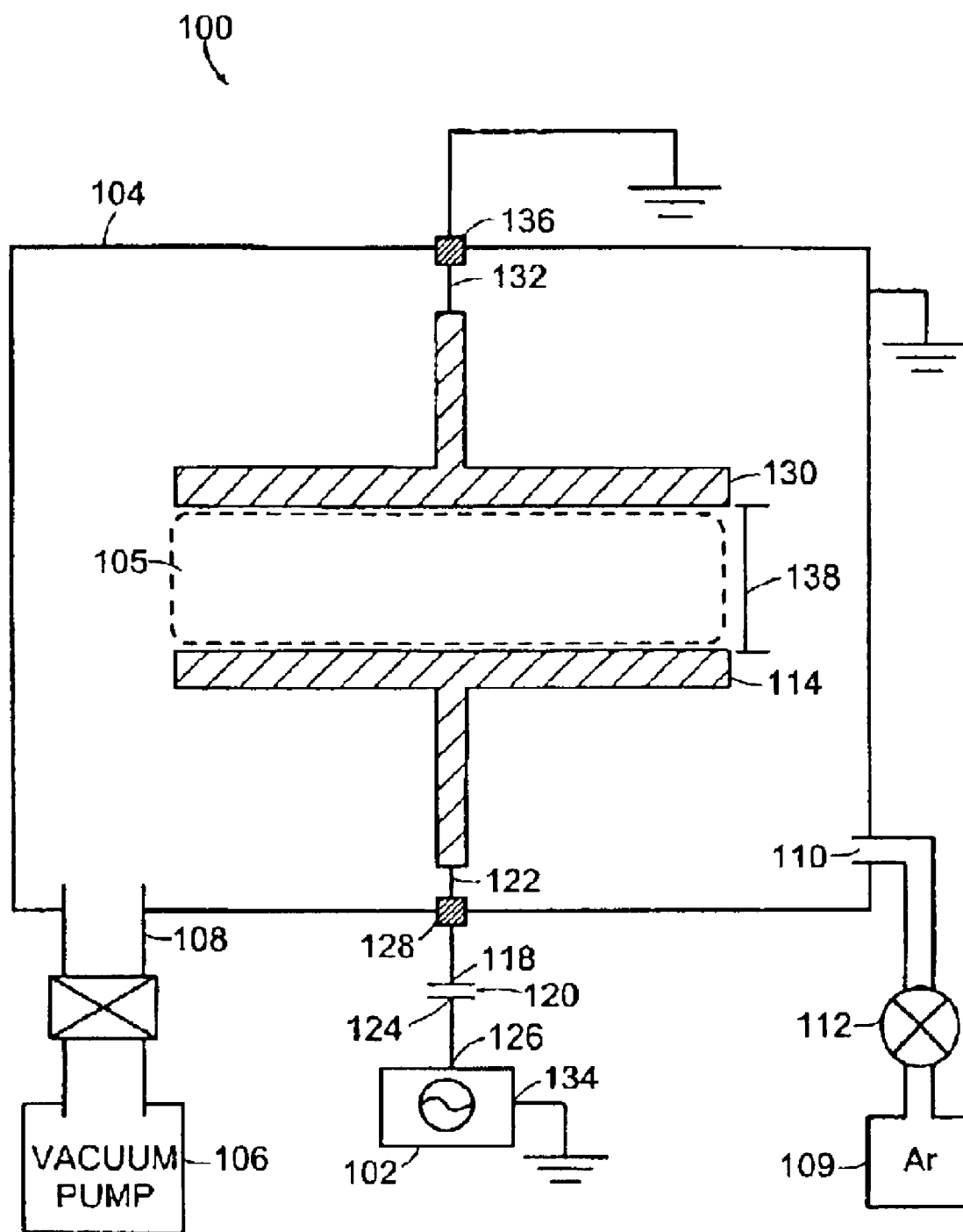


FIG. 1
PRIOR ART

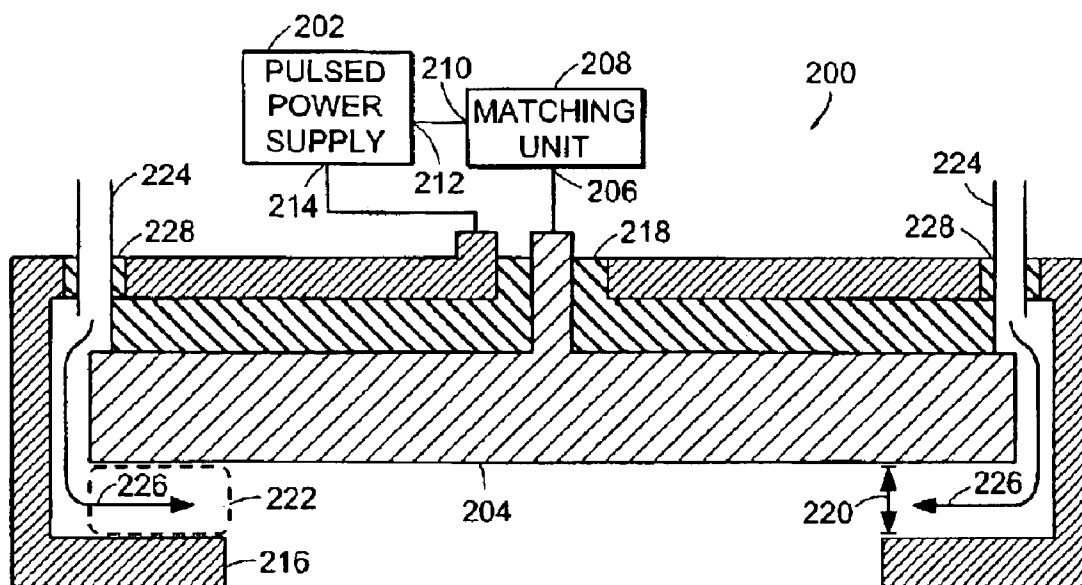


FIG. 2A

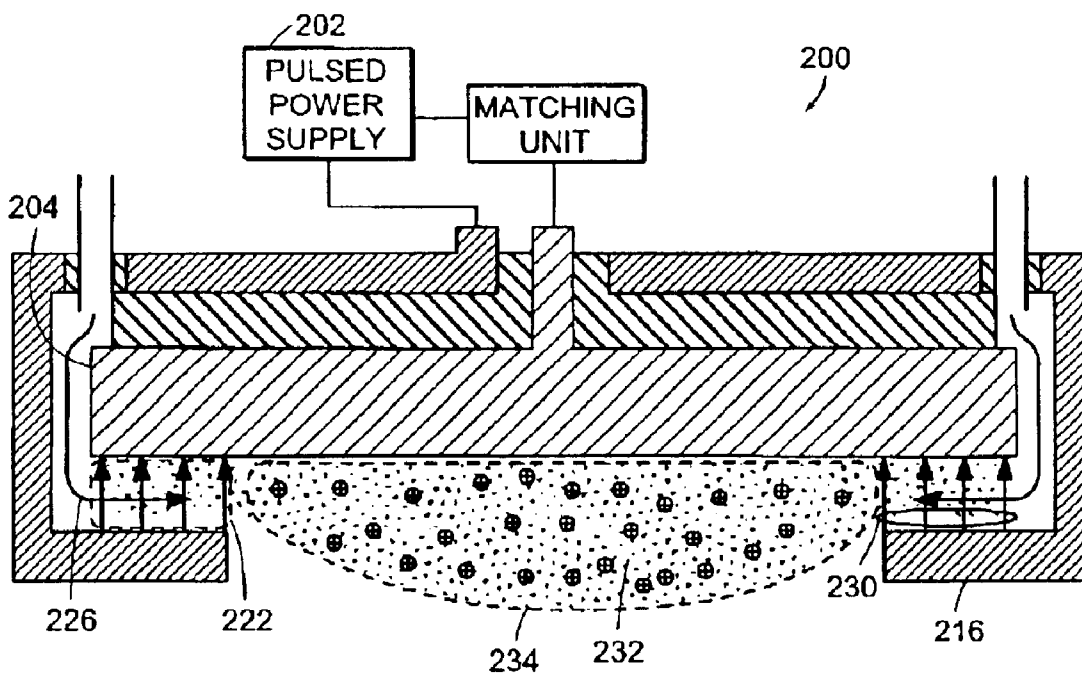


FIG. 2B

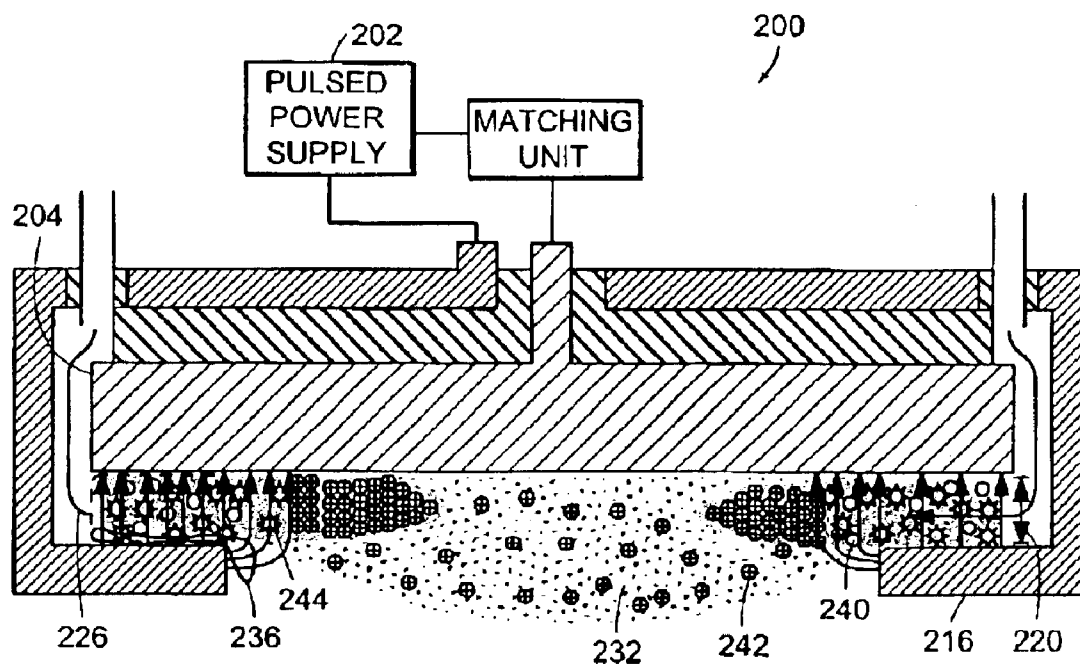


FIG. 2C

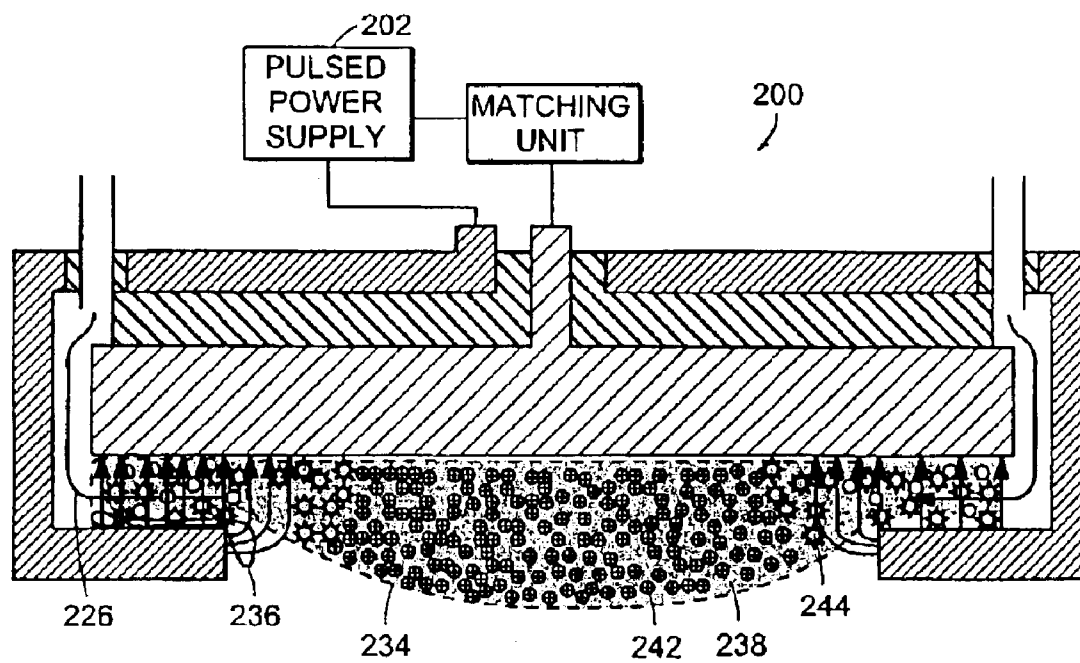


FIG. 2D

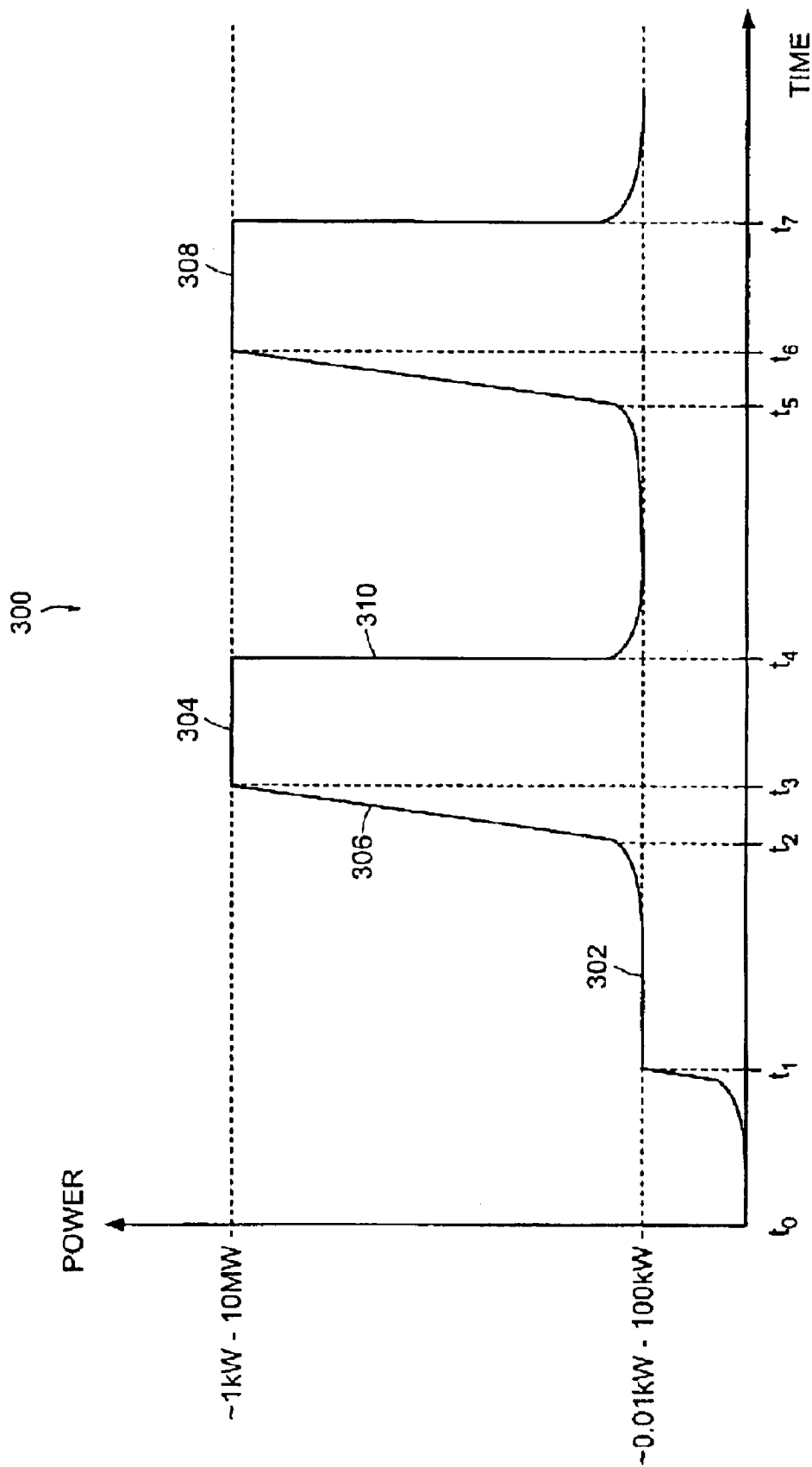


FIG. 3

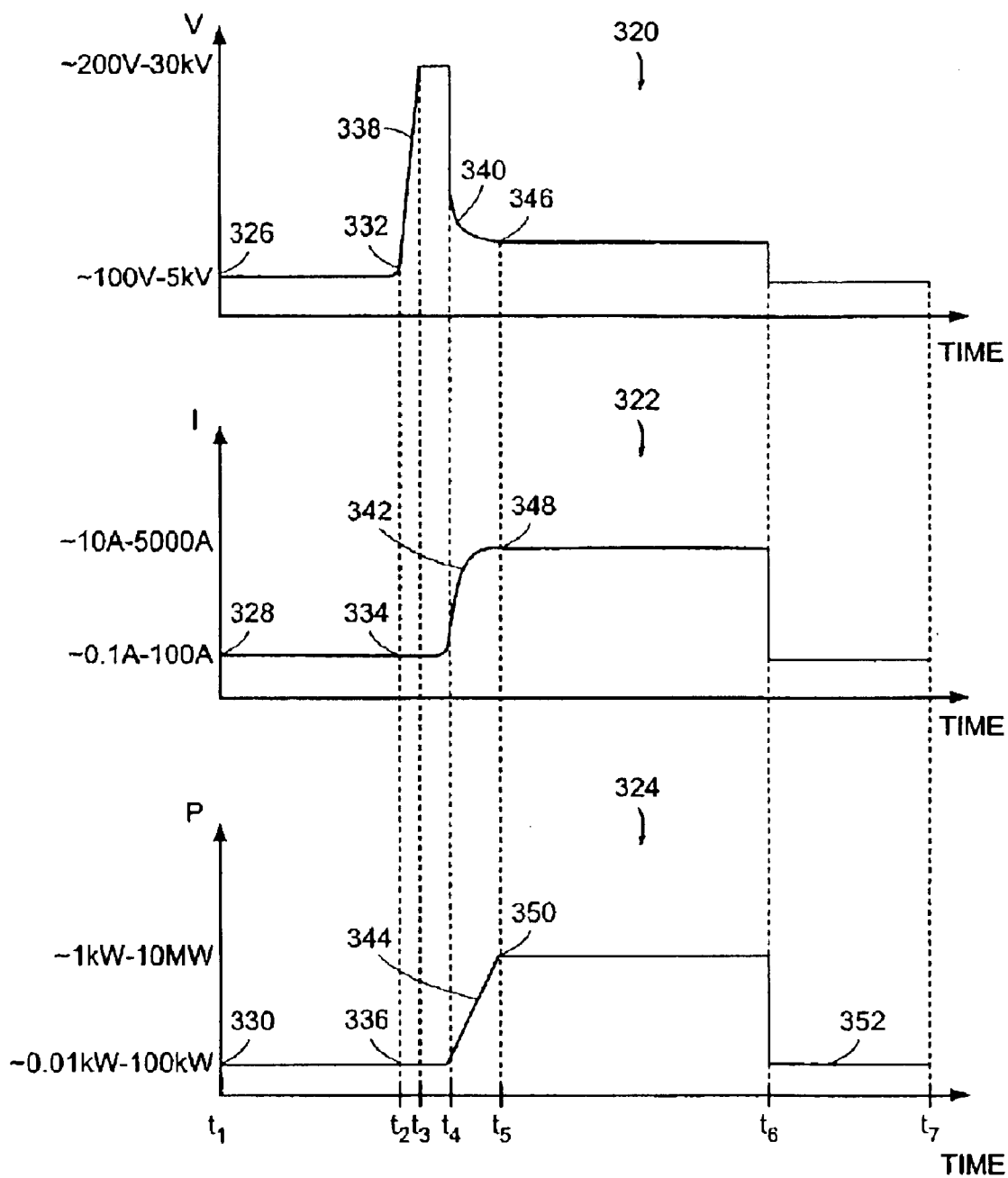


FIG. 4

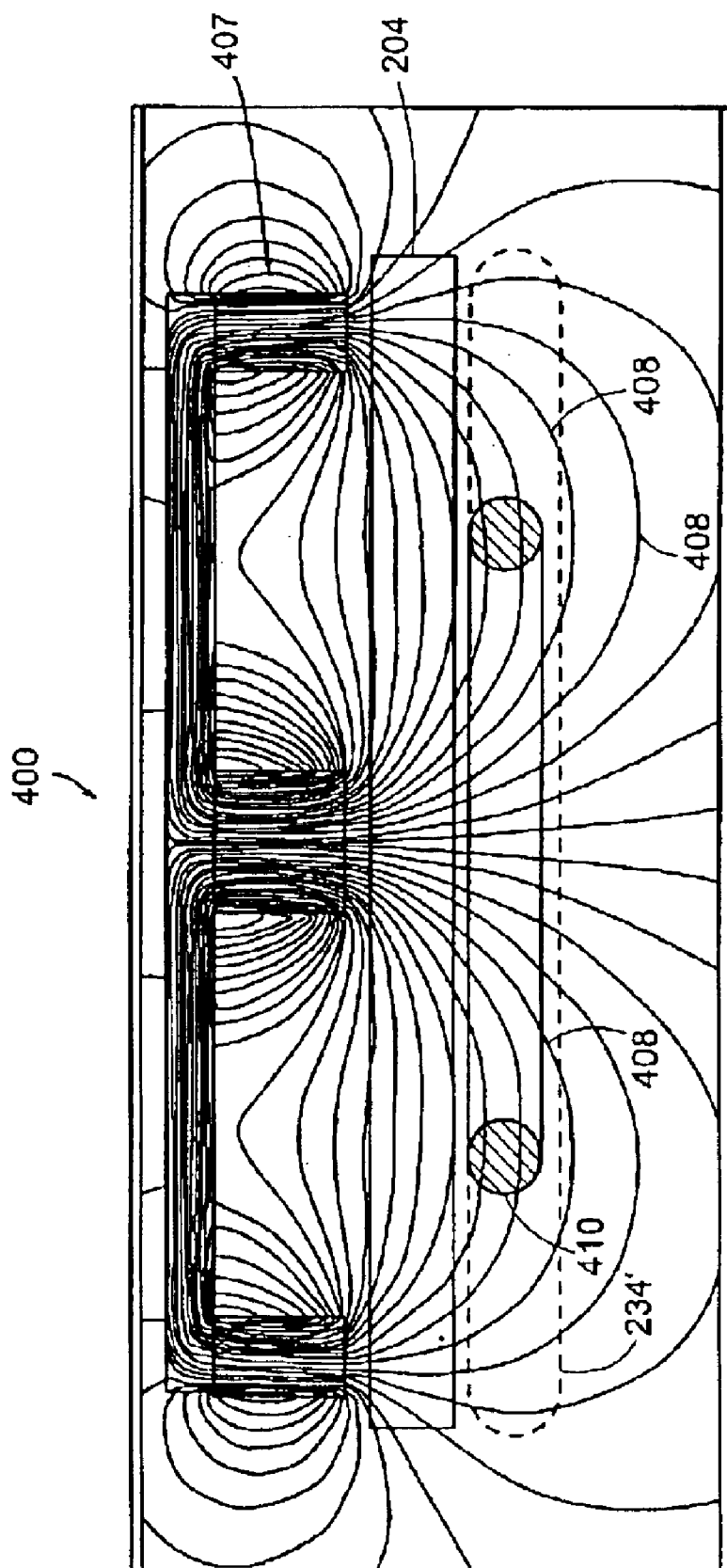


FIG. 5A

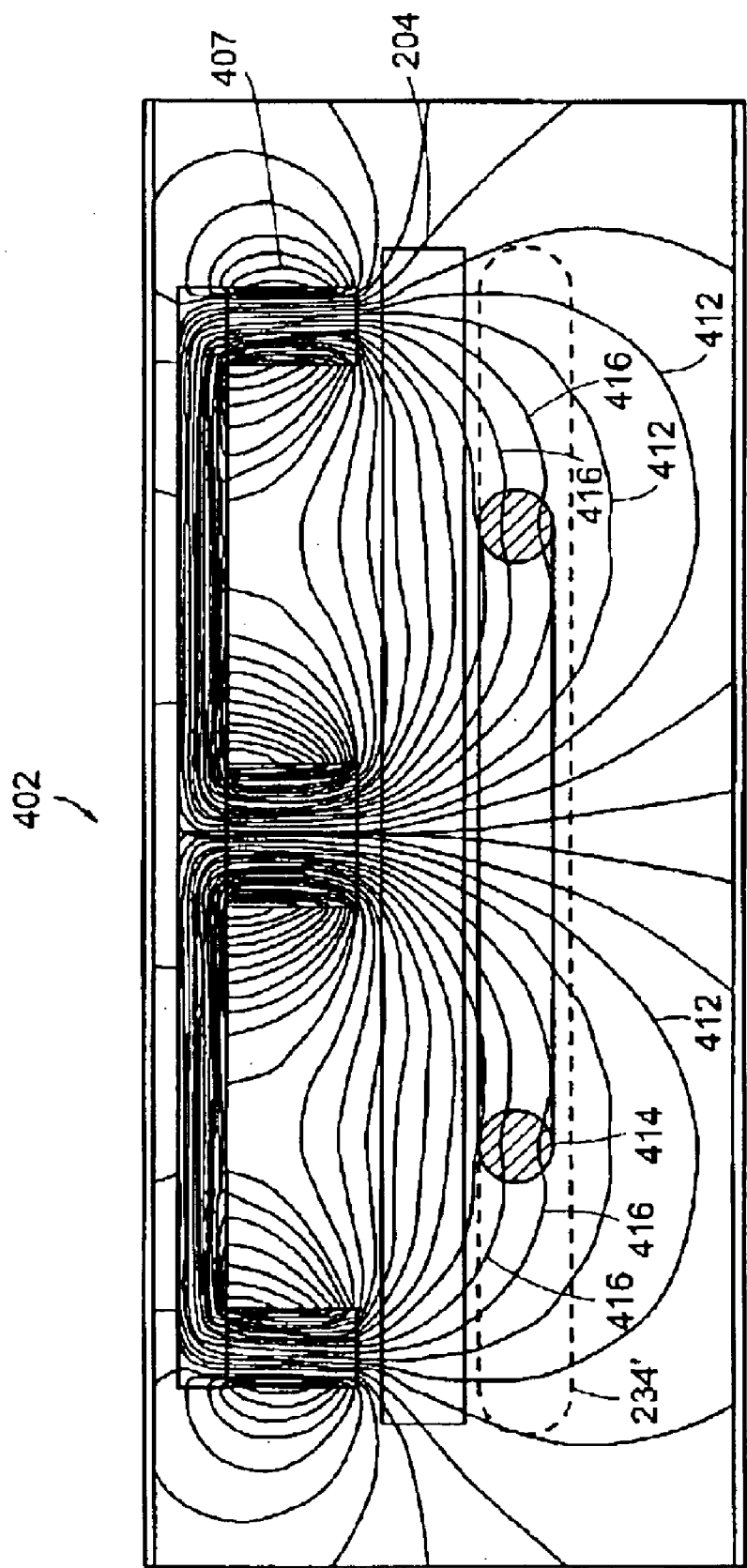


FIG. 5B

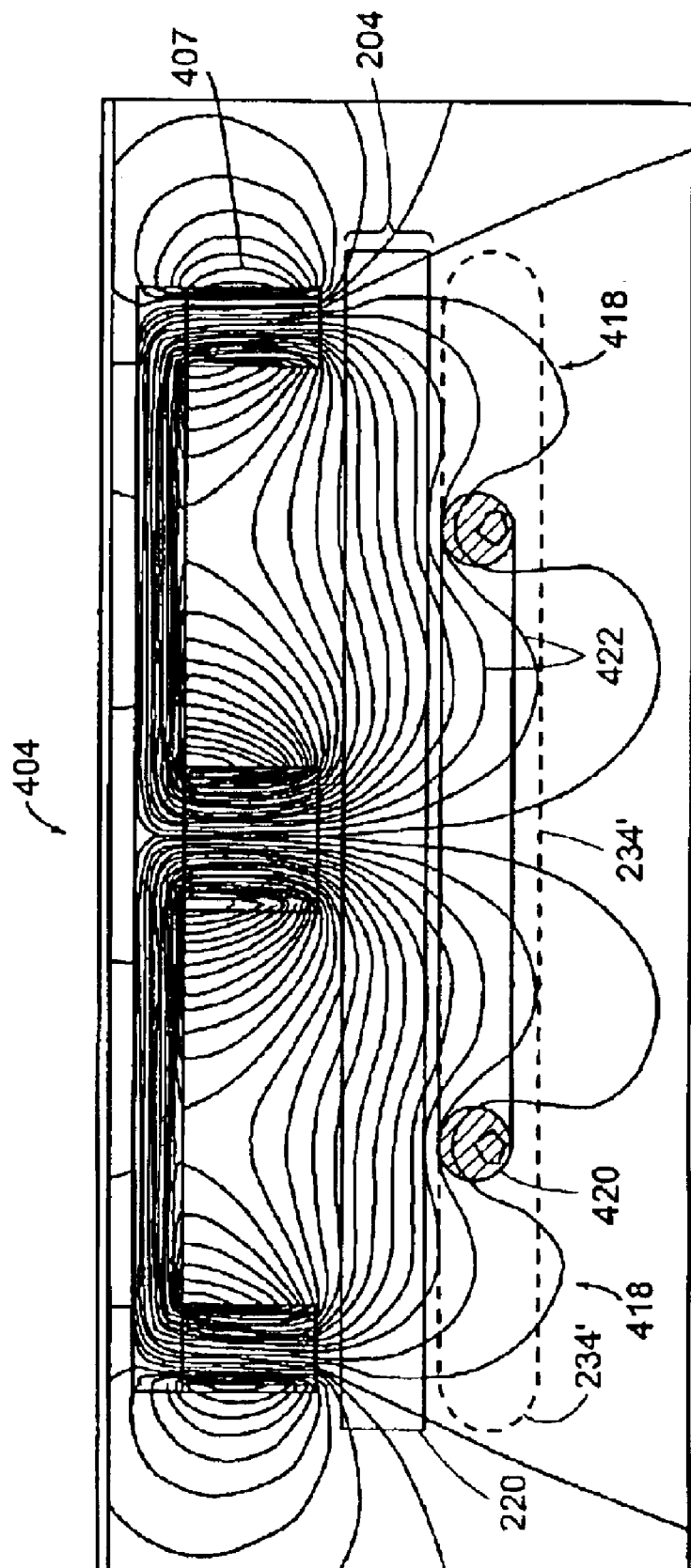


FIG. 5C

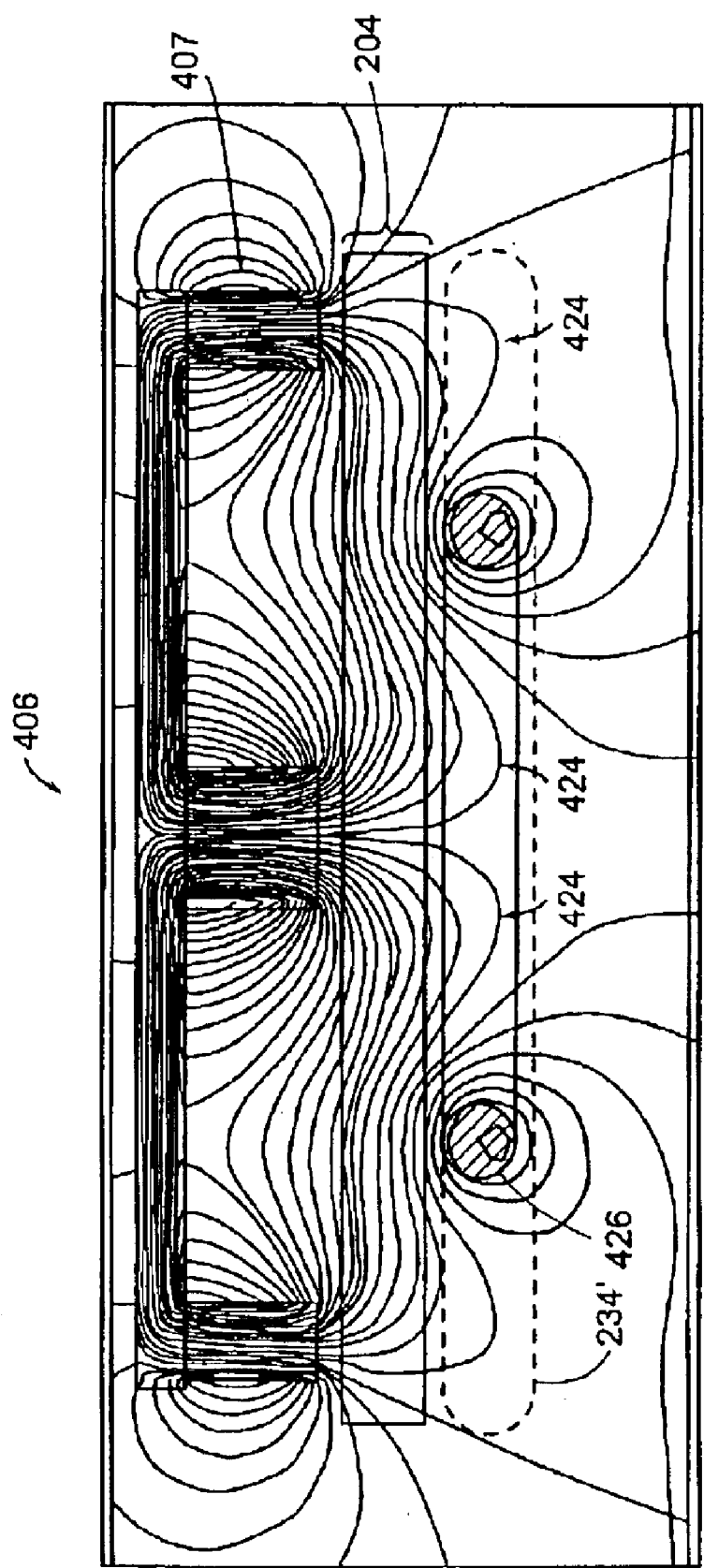


FIG. 5D

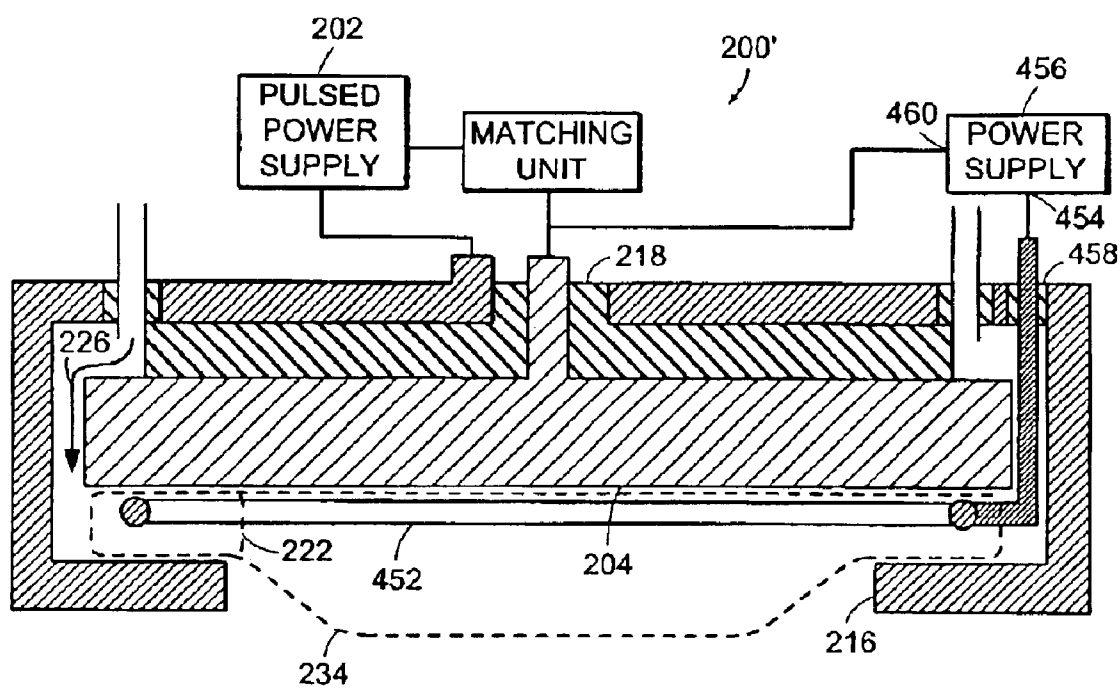


FIG. 6A

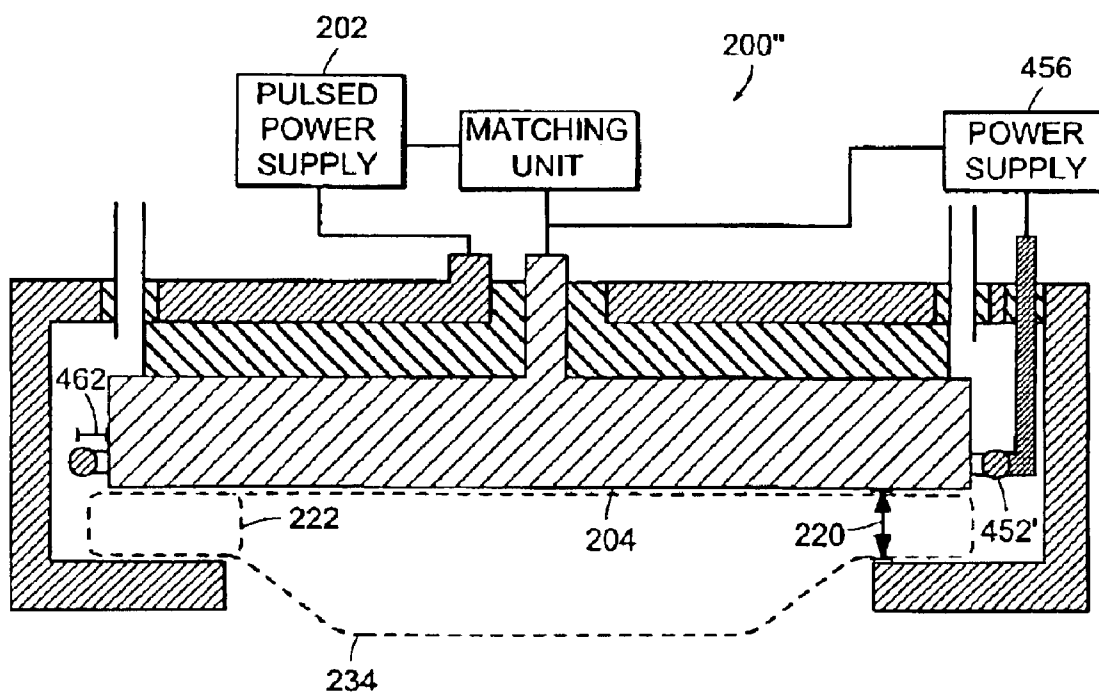


FIG. 6B

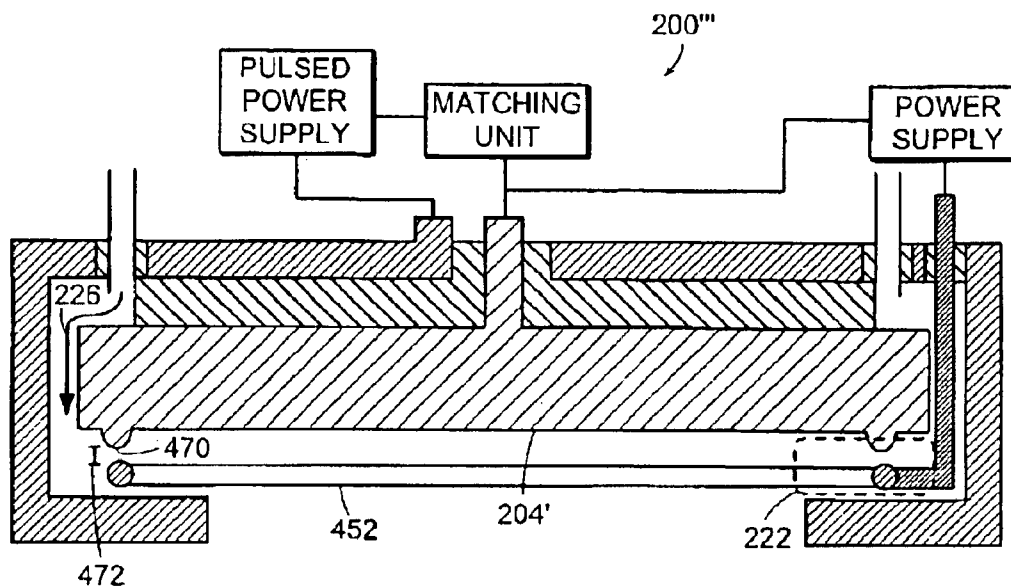


FIG. 6C

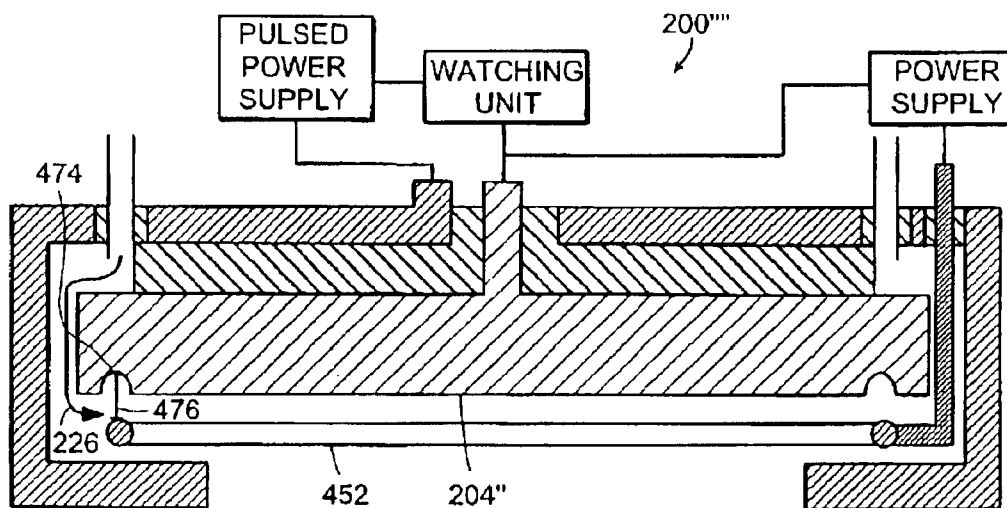


FIG. 6D

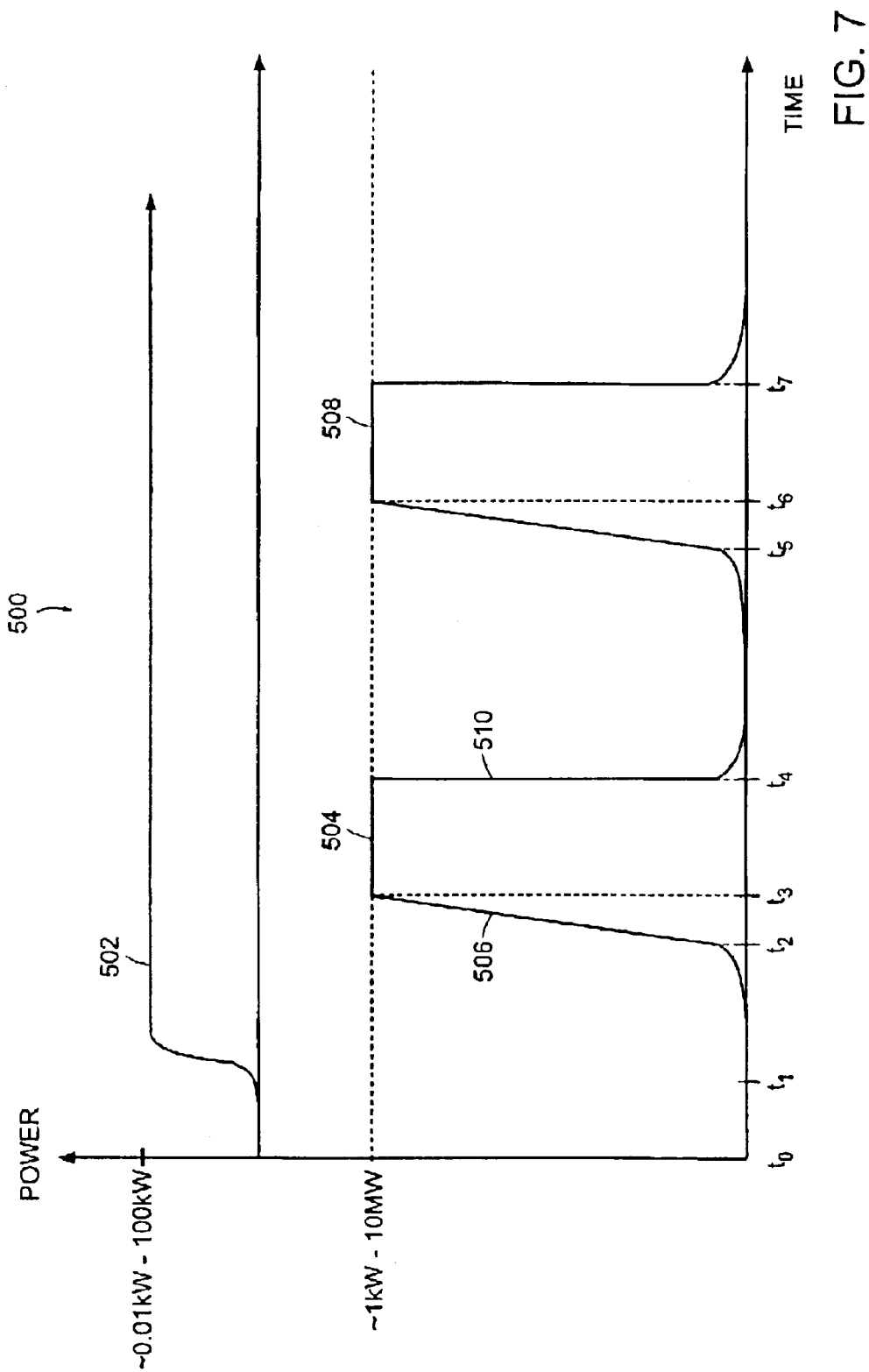


FIG. 7

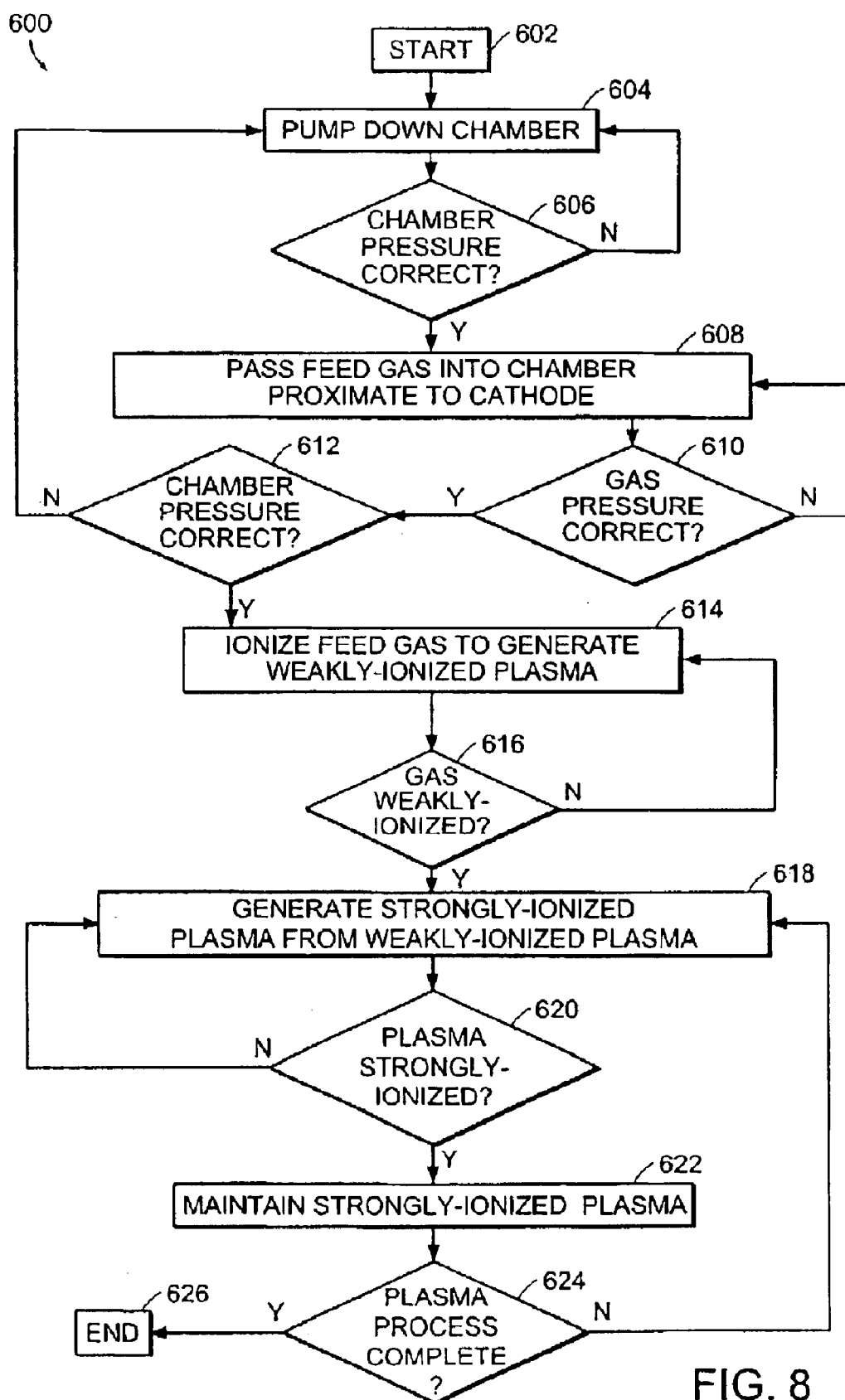


FIG. 8

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METHODS AND APPARATUS FOR GENERATING HIGH-DENSITY PLASMA

BACKGROUND OF INVENTION

Plasma is considered the fourth state of matter. A plasma is a collection of charged particles moving in random directions. A plasma is, on average, electrically neutral. One method of generating a plasma is to drive a current through a low-pressure gas between two parallel conducting electrodes. Once certain parameters are met, the gas "breaks down" to form the plasma. For example, a plasma can be generated by applying a potential of several kilovolts between two parallel conducting electrodes in an inert gas atmosphere (e.g., argon) at a pressure that is between about 10^{-1} and 10^{-2} Torr.

Plasma processes are widely used in many industries, such as the semiconductor manufacturing industry. For example, plasma etching is commonly used to etch substrate material and films deposited on substrates in the electronics industry. There are four basic types of plasma etching processes that are used to remove material from surfaces: sputter etching, pure chemical etching, ion energy driven etching, and ion inhibitor etching.

Plasma sputtering is a technique that is widely used for depositing films on substrates. Sputtering is the physical ejection of atoms from a target surface and is sometimes referred to as physical vapor deposition (PVD). Ions, such as argon ions, are generated and then are drawn out of the plasma, and are accelerated across a cathode dark space. The target has a lower potential than the region in which the plasma is formed. Therefore, the target attracts positive ions. Positive ions move towards the target with a high velocity. Positive ions impact the target and cause atoms to physically dislodge or sputter from the target. The sputtered atoms then propagate to a substrate where they deposit a film of sputtered target material. The plasma is replenished by electron-ion pairs formed by the collision of neutral molecules with secondary electrons generated at the target surface.

Magnetron sputtering systems use magnetic fields that are shaped to trap and to concentrate secondary electrons, which are produced by ion bombardment of the target surface. The plasma discharge generated by a magnetron sputtering system is located proximate to the surface of the target and has a high density of electrons. The high density of electrons causes ionization of the sputtering gas in a region that is close to the target surface.

BRIEF DESCRIPTION OF DRAWINGS

This invention is described with particularity in the detailed description. The above and further advantages of this invention may be better understood by referring to the following description in conjunction with the accompanying drawings, in which like numerals indicate like structural elements and features in various figures. The drawings are not necessarily to scale, emphasis instead being placed upon illustrating the principles of the invention.

FIG. 1 illustrates a cross-sectional view of a known plasma generating apparatus having a radio-frequency (RF) power supply.

FIG. 2A through FIG. 2D illustrate cross-sectional views of a plasma generating apparatus having a pulsed power supply according to one embodiment of the invention.

FIG. 3 illustrates a graphical representation of the pulse power as a function of time for periodic pulses applied to the plasma in the plasma generating apparatus of FIG. 2A.

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FIG. 4 illustrates graphical representations of the applied voltage, current, and power as a function of time for periodic pulses applied to the plasma in the plasma generating apparatus of FIG. 2A.

FIG. 5A through FIG. 5D illustrate various simulated magnetic field distributions proximate to the cathode for various electron $E \times B$ drift currents according to the present invention.

FIG. 6A through FIG. 6D illustrate cross-sectional views of various embodiments of plasma generating systems according to the present invention.

FIG. 7 illustrates a graphical representation of the pulse power as a function of time for periodic pulses applied to the plasma in the plasma generating system of FIG. 6A.

FIG. 8 is a flowchart of an illustrative method of generating a high-density plasma according to the present invention.

DETAILED DESCRIPTION

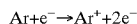
FIG. 1 illustrates a cross-sectional view of a known plasma generating apparatus **100** having a radio-frequency (RF) power supply **102**. The known plasma generating apparatus **100** includes a vacuum chamber **104** where the plasma **105** is generated. The vacuum chamber **104** is positioned in fluid communication with a vacuum pump **106** via a conduit **108**. The vacuum pump **106** is adapted to evacuate the vacuum chamber **104** to high vacuum. The pressure inside the vacuum chamber **104** is generally less than 10^{-1} Torr. A feed gas from a feed gas source **109**, such as an argon gas source, is introduced into the vacuum chamber **104** through a gas inlet **110**. The gas flow is controlled by a valve **112**.

The plasma generating apparatus **100** also includes a cathode **114**. The cathode **114** is generally in the shape of a circular disk. The cathode **114** is electrically connected to a first terminal **118** of a blocking capacitor **120** with an electrical transmission line **122**. A second terminal **124** of the blocking capacitor **120** is coupled to a first output **126** of the RF power supply **102**. An insulator **128** can be used to pass the electrical transmission line **122** through a wall of the vacuum chamber **104** in order to electrically isolate the cathode **114** from the vacuum chamber **104**.

An anode **130** is positioned in the vacuum chamber **104** proximate to the cathode **114**. The anode **130** is typically coupled to ground using an electrical transmission line **132**. A second output **134** of the RF power supply **102** is also typically coupled to ground. In order to isolate the anode **130** from the vacuum chamber **104**, an insulator **136** can be used to pass the electrical transmission line **132** through a wall of the vacuum chamber **104**. The vacuum chamber **104** can also be coupled to ground.

In operation, the RF power supply **102** applies a RF voltage pulse between the cathode **114** and the anode **130** that has a sufficient amplitude to ionize the argon feed gas in the vacuum chamber **104**. A typical RF driving voltage is between 100V and 1000V, and the distance **138** between the cathode **114** and the anode is between about 2 cm and 10 cm. Typical pressures are in the range of 10 mTorr to 100 mTorr. Typical power densities are in the range of 0.1 W/cm² to 1 W/cm². The driving frequency is typically 13.56 MHz. Typical plasma densities are in the range of 10^9 cm⁻³ to 10^{11} cm⁻³, and the electron temperature is on the order of 3 eV.

This typical ionization process is referred to as direct ionization or atomic ionization by electron impact and can be described as follows:



where Ar represents a neutral argon atom in the feed gas and e^- represents an ionizing electron generated in response to the voltage applied between the cathode 114 and the anode 130. The collision between the neutral argon atom and the ionizing electron results in an argon ion (Ar^+) and two electrons.

The plasma discharge is maintained, at least in part, by secondary electron emission from the cathode. However, typical operating pressures must be relatively high so that the secondary electrons are not lost to the anode 130 or the walls of the chamber 104. These pressures are not optimal for most plasma processes.

It is desirable to operate a plasma discharge at higher current densities, lower voltages, and lower pressures than can be obtained in a conventional glow discharge. This has led to the use of a DC magnetic field near the cathode 114 to confine the secondary electrons. Confining the secondary electrons substantially confines the plasma at a location (not shown) in the chamber 104 thereby increasing the plasma density at that location for a given input power, while reducing the overall loss area.

The magnetic confinement primarily occurs in a confinement region (not shown) where there is a relatively low magnetic field intensity. The shape and location of the confinement region depends on the design of the magnets. Generally, a higher concentration of positively charged ions in the plasma is present in the confinement region than elsewhere in the chamber 104. Consequently, the uniformity of the plasma can be severely diminished in magnetically enhanced systems.

The non-uniformity of the plasma in magnetron sputtering systems can result in undesirable non-uniform erosion of target material and thus relatively poor target utilization. The non-uniformity of the plasma in magnetron etching systems can result in non-uniform etching of a substrate.

Dramatically increasing the RF power applied to the plasma alone will not result in the formation of a more uniform and denser plasma. Furthermore, the amount of applied power necessary to achieve even an incremental increase in uniformity and density can increase the probability of generating an electrical breakdown condition leading to an undesirable electrical discharge (an electrical arc) in the chamber 104.

Pulsing direct current (DC) power applied to the plasma can be advantageous since the average discharge power can remain relatively low while relatively large power pulses are periodically applied. Additionally, the duration of these large voltage pulses can be preset so as to reduce the probability of establishing an electrical breakdown condition leading to an undesirable electrical discharge. An undesirable electrical discharge will corrupt the plasma process and can cause contamination in the vacuum chamber 104. However, very large power pulses can still result in undesirable electrical discharges regardless of their duration.

FIG. 2A through FIG. 2D illustrate cross-sectional views of a plasma generating apparatus 200 having a pulsed power supply 202 according to one embodiment of the invention. For example, FIG. 2A illustrates a cross-sectional view of a plasma generating apparatus 200 having a pulsed power supply 202 at a time before the pulsed power supply 202 is activated. In one embodiment, the plasma generating apparatus 200 includes a chamber (not shown), such as a vacuum chamber that supports the plasma. The chamber can be coupled to a vacuum system (not shown).

The plasma generating apparatus 200 also includes a cathode 204. In one embodiment, the cathode 204 can be

composed of a metal material such as stainless steel or any other material that does not chemically react with reactive gases. In another embodiment, the cathode 204 includes a target that can be used for sputtering. The cathode 204 is coupled to an output 206 of a matching unit 208. An input 210 of the matching unit 208 is coupled to a first output 212 of the pulsed power supply 202. A second output 214 of the pulsed power supply 202 is coupled to an anode 216. An insulator 218 isolates the anode 216 from the cathode 204.

In one embodiment, the first output 212 of the pulsed power supply 202 is directly coupled to the cathode 204 (not shown). In one embodiment (not shown), the second output 214 of the pulsed power supply 202 is coupled to ground. In this embodiment, the anode 216 is also coupled to ground.

In one embodiment (not shown), the first output 212 of the pulsed power supply 202 couples a negative voltage impulse to the cathode 204. In another embodiment (not shown), the second output 214 of the pulsed power supply 202 couples a positive voltage impulse to the anode 216.

In one embodiment, the pulsed power supply 202 generates peak voltage levels of up to about 30,000V. Typical operating voltages are generally between about 50V and 30 kV. In one embodiment, the pulsed power supply 202 generates peak current levels of less than 1 A to about 5,000 A or more depending on the volume of the plasma. Typical operating currents varying from less than one hundred amperes to more than a few thousand amperes depending on the volume of the plasma. In one embodiment, the pulses generated by the pulsed power supply 202 have a repetition rate that is below 1 kHz. In one embodiment, the pulse width of the pulses generated by the pulsed power supply 202 is substantially between about one microsecond and several seconds.

The anode 216 is positioned so as to form a gap 220 between the anode 216 and the cathode 204 that is sufficient to allow current to flow through a region 222 between the anode 216 and the cathode 204. In one embodiment, the width of the gap 220 is between approximately 0.3 cm and 10 cm. The surface area of the cathode 204 determines the volume of the region 222. The gap 220 and the total volume of the region 222 are parameters in the ionization process as described herein.

In one embodiment, the plasma generating apparatus 200 includes a chamber (not shown), such as a vacuum chamber. The chamber is coupled in fluid communication to a vacuum pump (not shown) through a vacuum valve (not shown). In one embodiment, the chamber (not shown) is electrically coupled to ground potential. One or more gas lines 224 provide feed gas 226 from a feed gas source (not shown) to the chamber. In one embodiment, the gas lines 224 are isolated from the chamber and other components by insulators 228. In other embodiments, the gas lines 224 can be isolated from the feed gas source using in-line insulating couplers (not shown). The gas source can be any feed gas 226 including but not limited to argon. In some embodiments, the feed gas 226 can include a mixture of different gases, reactive gases, or pure reactive gas gases. In some embodiments, the feed gas 226 includes a noble gas or a mixture of gases.

In operation, the feed gas 226 from the gas source is supplied to the chamber by a gas flow control system (not shown). Preferably, the feed gas 226 is supplied between the cathode 204 and the anode 216. Directly injecting the feed gas 226 between the cathode 204 and the anode 216 can increase the flow rate of the feed gas 226. This causes a rapid volume exchange in the region 222 between the cathode 204 and the anode 216, which permits a high-power pulse having

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a longer duration to be applied across the gap 220. The longer duration high-power pulse results in the formation of a higher density plasma. This volume exchange is described herein in more detail.

In one embodiment, the pulsed power supply 202 is a component in an ionization source that generates a weakly-ionized plasma 232. Referring to FIG. 2B, after the feed gas is supplied between the cathode 204 and the anode 216, the pulsed power supply 202 applies a voltage pulse between the cathode 204 and the anode 216. In one embodiment, the pulsed power supply 202 applies a negative voltage pulse to the cathode 204. The size and shape of the voltage pulse are chosen such that an electric field 230 develops between the cathode 204 and the anode 216. The amplitude and shape of the electric field 230 are chosen such that a weakly-ionized plasma 232 is generated in the region 222 between the anode 216 and the cathode 204.

The weakly-ionized plasma 232 is also referred to as a pre-ionized plasma. In one embodiment, the peak plasma density of the pre-ionized plasma is between about 10^6 and 10^{12} cm⁻³ for argon feed gas. The pressure in the chamber can vary from about 10^{-3} to 10 Torr or higher. The pressure can vary depending on various system parameters, such as the presence of a magnetic field proximate to the cathode 204. The peak plasma density of the weakly-ionized plasma 232 depends on the properties of the specific plasma generating system and is a function of the location of the measurement in the weakly-ionized plasma 232.

In one embodiment, to generate the weakly-ionized plasma 232, the pulsed power supply 202 generates a low power pulse having an initial voltage of between about 100V and 5 kV with a discharge current of between about 0.1 A and 100 A. In some embodiments, the width of the pulse can be in on the order of 0.1 microseconds up to one hundred seconds. Specific parameters of the pulse are discussed herein in more detail.

In one embodiment, prior to the generation of the weakly-ionized plasma 232, the pulsed power supply 202 generates a potential difference between the cathode 204 and the anode 216 before the feed gas 226 is supplied between the cathode 204 and the anode 216. In another embodiment, the pulsed power supply 202 generates a current through the gap 220 after the feed gas 226 is supplied between the cathode 204 and the anode 216.

In another embodiment, a direct current (DC) power supply (not shown) is used in an ionization source to generate and maintain the weakly-ionized or pre-ionized plasma 232. In this embodiment, the DC power supply is adapted to generate a voltage that is large enough to ignite the weakly-ionized plasma 232. In one embodiment, the DC power supply generates an initial voltage of several kilovolts that creates a plasma discharge voltage on the order of between about 100V and 1 kV with a discharge current in the range of about 0.1 A and 100 A between the cathode 204 and the anode 216 in order to generate and maintain the weakly-ionized plasma 232. The value of the discharge current depends on the power level of the power supply and is a function of the volume of the weakly-ionized plasma 232. Furthermore, the presence of a magnetic field (not shown) in the region 222 can have a dramatic effect on the value of the applied voltage and current required to generate the weakly-ionized plasma 232.

In some embodiments (not shown), the DC power supply generates a current that is between about 1 mA and 100 A depending on the size of the plasma generating system and the strength of a magnetic field in a region 234. In one embodiment, before generating the weakly-ionized plasma

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232, the DC power supply is adapted to generate and maintain an initial peak voltage between the cathode 204 and the anode 216 before the introduction of the feed gas 226.

In another embodiment, an alternating current (AC) power supply (not shown) is used to generate and maintain the weakly-ionized or pre-ionized plasma 232. For example, the weakly-ionized or pre-ionized plasma 232 can be generated and maintained using electron cyclotron resonance (ECR), capacitively coupled plasma discharge (CCP), or inductively coupled plasma (ICP) discharge.

AC power supplies can require less power to generate and maintain a weakly-ionized plasma than a DC power supply. In addition, the pre-ionized or weakly-ionized plasma 232 can be generated by numerous other techniques, such as UV radiation techniques, X-ray techniques, electron beam techniques, ion beam techniques, or ionizing filament techniques. These techniques include components used in ionization sources according to the invention. In some embodiments, the weakly-ionized plasma is formed outside of the region 222 and then diffuses into the region 222.

Forming the weakly-ionized or pre-ionized plasma 232 substantially eliminates the probability of establishing a breakdown condition in the chamber when high-power pulses are applied between the cathode 204 and the anode 216. The probability of establishing a breakdown condition is substantially eliminated because the weakly-ionized plasma 232 has a low-level of ionization that provides electrical conductivity through the plasma. This conductivity substantially prevents the setup of a breakdown condition, even when high power is applied to the plasma.

In one embodiment, as the feed gas 226 is pushed through the region 222, the weakly-ionized plasma 232 diffuses somewhat homogeneously through the region 234. This homogeneous diffusion tends to facilitate the creation of a highly uniform strongly-ionized plasma in the region 234.

In one Embodiment (not show), the weakly-ionized plasma can be trapped proximate to the cathode 204 by a magnetic field. Specifically, electrons in the weakly-ionized plasma 232 can be trapped by a magnetic field generated proximate to the cathode 204. In one embodiment, the strength of the magnetic field is between about fifty and two thousand gauss.

In one embodiment, a magnet assembly (not shown) generates the magnet field located proximate to the cathode 204. The magnet assembly can include permanent magnets (not shown), or alternatively, electro-magnets (not shown). The configuration of the magnet assembly can be varied depending on the desired shape and strength of the magnetic field. In alternate embodiments, the magnet assembly can have either a balanced or unbalanced configuration. In one embodiment, the magnet assembly includes switching electro-magnets, which generate a pulsed magnetic field proximate to the cathode 204. In some embodiments, additional magnet assemblies (not shown) can be placed at various locations around and throughout the chamber (not shown).

Referring to FIG. 2C, once the weakly-ionized plasma 232 is formed, the pulsed power supply 202 generates high-power pulses between the cathode 204 and the anode 216 (FIG. 2C). The desired power level of the high-power pulses depends on several factors including the density of the weakly-ionized plasma 232, and the volume of the plasma, for example. In one embodiment, the power level of the high-power pulse is in the range of about 1 kW to about 10 MW or higher.

Each of the high-power pulses is maintained for a predetermined time that, in some embodiments, is approximately

one microsecond to ten seconds. The repetition frequency or repetition rate of the high-power pulses, in some embodiments, is in the range of between about 0.1 Hz to 1 kHz. The average power generated by the pulsed power supply **202** can be less than one megawatt depending on the volume of the plasma. In one embodiment, the thermal energy in the cathode **204** and/or the anode **216** is conducted away or dissipated by liquid or gas cooling such as helium cooling (not shown).

The high-power pulses generate a strong electric field **236** between the cathode **204** and the anode **216**. The strong electric field **236** is substantially located in the region **222** between the cathode **204** and the anode **216**. In one embodiment, the electric field **236** is a pulsed electric field. In another embodiment, the electric field **236** is a quasi-static electric field. By quasi-static electric field we mean an electric field that has a characteristic time of electric field variation that is much greater than the collision time for electrons with neutral gas particles. Such a time of electric field variation can be on the order of ten seconds. The strength and the position of the strong electric field **236** will be discussed in more detail herein.

Referring to FIG. 2D, the high-power pulses generate a highly-ionized or a strongly-ionized plasma **238** from the weakly-ionized plasma **232** (FIG. 2C). The strongly-ionized plasma **238** is also referred to as a high-density plasma. The discharge current that is formed from the strongly-ionized plasma **238** can be on the order of about 5 kA or more with a discharge voltage in the range of between about 50V and 500V for a pressure that is on the order of between about 100 mTorr and 10 Torr.

In one embodiment, the strongly-ionized plasma **238** tends to diffuse homogeneously in the region **234**. The homogenous diffusion creates a more homogeneous plasma volume. Homogenous diffusion is described in more detail with reference to FIG. 5A through FIG. 5D.

Homogeneous diffusion is advantageous for many plasma processes. For example, plasma etching processes having homogenous diffusion accelerate ions in the strongly-ionized plasma **238** towards the surface of the substrate (not shown) being etched in a more uniform manner than with conventional plasma etching. Consequently, the surface of the substrate is etched more uniformly. Plasma processes having homogeneous diffusion can achieve high uniformity without the necessity of rotating the substrate.

Also, magnetron sputtering systems having homogenous diffusion accelerate ions in the strongly-ionized plasma **238** towards the surface of the sputtering target in a more uniform manner than with conventional magnetron sputtering. Consequently, the target material is deposited more uniformly on a substrate without the necessity of rotating the substrate and/or the magnetron. Also, the surface of the sputtering target is eroded more evenly and, thus higher target utilization is achieved.

In one embodiment, the plasma generating apparatus **200** of the present invention generates a relatively high electron temperature plasma and a relatively high-density plasma. One application for the strongly-ionized plasma **238** of the present invention is ionized physical vapor deposition (IPVD) (not shown), which is a technique that converts neutral sputtered atoms into positive ions to enhance a sputtering process.

Referring again to FIG. 2D, the strong electric field **236** facilitates a multi-step ionization process of the feed gas **226** that substantially increases the rate at which the strongly-ionized plasma **238** is formed. In one embodiment, the feed gas is a molecular gas and the strong electric field **236**

enhances the formation of ions in the plasma. The multi-step or stepwise ionization process is described as follows.

A pre-ionizing voltage is applied between the cathode **204** and the anode **216** across the feed gas **226** to form the weakly-ionized plasma **232**. The weakly-ionized plasma **232** is generally formed in the region **222** and diffuses to the region **234** as the feed gas **226** continues to flow. In one embodiment (not shown) a magnetic field is generated in the region **222** and extends to the center of the cathode **204**. This magnetic field tends to assist in diffusing electrons from the region **222** to the region **234**. The electrons in the weakly-ionized plasma **232** are substantially trapped in the region **234** by the magnetic field. In one embodiment, the volume of weakly-ionized plasma in the region **222** is rapidly exchanged with a new volume of feed gas **226**.

After the formation of the weakly-ionized plasma **232** (FIG. 2C), the pulsed power supply **202** applies a high-power pulse between the cathode **204** and the anode **216**. This high-power pulse generates the strong electric field **236** in the region **222** between the cathode **204** and the anode **216**. The strong electric field **236** results in collisions occurring between neutral atoms **240**, electrons (not shown), and ions **242** in the weakly-ionized plasma **232**. These collisions generate numerous excited atoms **244** in the weakly-ionized plasma **232**.

The accumulation of excited atoms **244** in the weakly-ionized plasma **232** alters the ionization process. In one embodiment, the strong electric field **236** facilitates a multi-step ionization process of an atomic feed gas that significantly increases the rate at which the strongly-ionized plasma **238** is formed. The multi-step ionization process has an efficiency that increases as the density of excited atoms **244** in the weakly-ionized plasma **232** increases. The strong electric field **236** enhances the formation of ions of a molecular or atomic feed gas.

In one embodiment, the distance or gap **220** between the cathode **204** and the anode **216** is chosen so as to maximize the rate of excitation of the atoms. The value of the electric field **236** in the region **222** depends on the voltage level applied by the pulsed power supply **202** and the size of the gap **220** between the anode **216** and the cathode **204**. In some embodiments, the strength of the electric field **236** can vary between about 2V/cm and 10⁵V/cm depending on various system parameters and operating conditions of the plasma system.

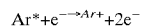
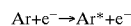
In some embodiments, the gap **220** can be between about 0.30 cm and about 10 cm depending on various parameters of the desired plasma. In one embodiment, the electric field **236** in the region **222** is rapidly applied to the pre-ionized or weakly-ionized plasma **232**. In some embodiments, the rapidly applied electric field **236** is generated by applying a voltage pulse having a rise time that is between about 0.1 microsecond and ten seconds.

In one embodiment, the dimensions of the gap **220** and the parameters of the applied electric field **236** are varied in order to determine the optimum condition for a relatively high rate of excitation of the atoms **240** in the region **222**. For example, an argon atom requires an energy of about 11.55 eV to become excited. Thus, as the feed gas **226** flows through the region **222**, the weakly-ionized plasma **232** is formed and the atoms **240** in the weakly-ionized plasma **232** experience a stepwise ionization process.

The excited atoms **244** in the weakly-ionized plasma **232** then encounter the electrons (not shown) that are in the region **234**. The excited atoms **244** only require about 4 eV of energy to ionize while neutral atoms **240** require about 15.76 eV of energy to ionize. Therefore, the excited atoms

244 will ionize at a much higher rate than the neutral atoms 240. In one embodiment, ions 242 in the strongly-ionized plasma 238 strike the cathode 204 causing secondary electron emission from the cathode 204. These secondary electrons interact with neutral 240 or excited atoms 244 in the strongly-ionized plasma 238. The process further increases the density of ions 242 in the strongly-ionized plasma 238 as the feed gas 226 is exchanged.

The multi-step ionization process corresponding to the rapid application of the electric field 236 can be described as follows:



where Ar represents a neutral argon atom 240 in the feed gas 226 and e^- represents an ionizing electron generated in response to a pre-ionized plasma 232, when sufficient voltage is applied between the cathode 204 and the anode 216. Additionally, Ar^* represents an excited argon atom 244 in the weakly-ionized plasma 232. The collision between the excited argon atom 244 and the ionizing electron results in an argon ion (Ar^+) and two electrons.

The excited argon atoms 244 generally require less energy to become ionized than neutral argon atoms 240. Thus, the excited atoms 244 tend to more rapidly ionize near the surface of the cathode 204 than the neutral argon atoms 240. As the density of the excited atoms 244 in the plasma increases, the efficiency of the ionization process rapidly increases. This increased efficiency eventually results in an avalanche-like increase in the density of the strongly-ionized plasma 238. Under appropriate excitation conditions, the proportion of the energy applied to the weakly-ionized plasma 232, which is transformed to the excited atoms 244, is very high for a pulsed discharge in the feed gas 226.

Thus, in one aspect of the invention, high-power pulses are applied to a weakly-ionized plasma 232 across the gap 220 to generate the strong electric field 236 between the anode 216 and the cathode 204. This strong electric field 236 generates excited atoms 244 in the weakly-ionized plasma 232. The excited atoms 244 are rapidly ionized by interactions with the secondary electrons that are emitted by the cathode 204. The rapid ionization results in a strongly-ionized plasma 238 having a large ion density being formed in the area 234 proximate to the cathode 204. The strongly-ionized plasma 238 is also referred to as a high-density plasma.

In one embodiment of the invention, a higher density plasma is generated by controlling the flow of the feed gas 226 in the region 222. In this embodiment, a first volume of feed gas 226 is supplied to the region 222. The first volume of feed gas 226 is then ionized to form a weakly-ionized plasma 232 in the region 222. Next, the pulsed power supply 202 applies a high-power electrical pulse across the weakly-ionized plasma 232. The high-power electrical pulse generates a strongly-ionized plasma 238 from the weakly-ionized plasma 232.

The level and duration of the high-power electrical pulse is limited by the level and duration of the power that the strongly-ionized plasma 238 can absorb before the high-power discharge contracts and terminates. In one embodiment, the strength and the duration of the high-power electrical pulse are increased and thus the density of the strongly-ionized plasma 238 is increased by increasing the flow rate of the feed gas 226.

In one embodiment, the strongly-ionized plasma 238 is transported through the region 222 by a rapid volume

exchange of feed gas 226. As the feed gas 226 moves through the region 222, it interacts with the moving strongly-ionized plasma 238 and also becomes strongly-ionized from the applied high-power electrical pulse. The ionization process can be a combination of direct ionization and/or stepwise ionization as described herein. Transporting the strongly-ionized plasma 238 through the region 222 by a rapid volume exchange of the feed gas 226 increases the level and the duration of the power that can be applied to the strongly-ionized plasma 238 and, thus, generates a higher density strongly-ionized plasma in the region 234.

The efficiency of the ionization process can be increased by applying a magnetic field (not shown) proximate to the cathode 204, as described herein. The magnetic field tends to trap electrons in the weakly-ionized plasma 232 and also tends to trap secondary electrons proximate to the cathode 204. The trapped electrons ionize the excited atoms 244 generating the strongly-ionized plasma 238. In one embodiment, the magnetic field is generated in the region 222 to substantially trap electrons in the area where the weakly-ionized plasma 232 is ignited.

In one embodiment, the plasma generating system 200 can be configured for plasma etching. In another embodiment, the plasma generating system 200 can be configured for plasma sputtering. In particular, the plasma generating system 200 can be used for sputtering magnetic materials. Known magnetron sputtering systems generally are not suitable for sputtering magnetic materials because the magnetic field generated by the magnetron can be absorbed by the magnetic target material. RF diode sputtering is sometimes used to sputter magnetic materials. However, RF diode sputtering generally has poor film thickness uniformity and relatively low deposition rates.

The plasma generating system 200 can be adapted to sputter magnetic materials by including a target assembly having a magnetic target material and by driving that target assembly with an RF power supply (not shown). For example, an RF power supply can provide an RF power that is on order of about 10 kW. A substantially uniform weakly-ionized plasma can be generated by applying RF power across a feed gas that is located proximate to the target assembly. The strongly-ionized plasma is generated by applying a strong electric field across the weakly-ionized plasma as described herein. The RF power supply applies a negative voltage bias to the target assembly. Ions in the strongly-ionized plasma bombard the target material thereby causing sputtering.

The plasma generating system 200 can also be adapted to sputter dielectric materials. Dielectric materials can be sputtered by driving a target assembly including a dielectric target material with an RF power supply (not shown). For example, an RF power supply can provide an RF power that is on order of about 10 kW. A substantially uniform weakly-ionized plasma can be generated by applying RF power across a feed gas that is located proximate to the target assembly.

In another embodiment, a DC power supply (not shown) is used to create a weakly-ionized plasma 232 according to the present invention. In this embodiment, the dielectric target material is positioned relative to the cathode 204 such that an area of the cathode 204 can conduct a direct current between the anode 216 and the cathode 204.

In one embodiment, a magnetic field is generated proximate to the target assembly in order to trap electrons in the weakly-ionized plasma. The strongly-ionized plasma is generated by applying a strong electric field across the weakly-ionized plasma as described herein. The RF power supply

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applies a negative voltage bias to the target assembly. Ions in the strongly-ionized plasma bombard the target material thereby causing sputtering.

In one embodiment, a strongly-ionized plasma **238** according to the present invention is used to generate an ion beam. An ion beam source according to the present invention includes the plasma generating apparatus described herein and an additional electrode (not shown) that is used to accelerate ions in the plasma. In one embodiment, the external electrode is a grid. The ion beam source according to the present invention can generate a very high-density ion flux. For example, the ion beam source can generate ozone flux. Ozone is a highly reactive oxidizing agent that can be used for many applications such as cleaning process chambers, deodorizing air, purifying water, and treating industrial wastes.

FIG. 3 illustrates a graphical representation **300** of the applied power of a pulse as a function of time for periodic pulses applied to the plasma in the plasma generating apparatus **200** of FIG. 2A. At time t_0 , the feed gas **226** flows between the cathode **204** and the anode **216** before the pulsed power supply **202** is activated. The time required for a sufficient quantity of gas **226** to flow between the cathode **204** and the anode **216** depends on several factors including the flow rate of the gas **226** and the desired pressure in the region **222**.

In one embodiment (not shown), the pulsed power supply **202** is activated before the feed gas **226** flows into the region **222**. In this embodiment, the feed gas **226** is injected between the anode **216** and the cathode **204** where it is ignited by the pulsed power supply **202** to generate the weakly-ionized plasma **232**.

In one embodiment, the feed gas **226** flows between the anode **216** and the cathode **204** between time t_0 and time t_1 . At time t_1 , the pulsed power supply **202** generates a pulse **302** between the cathode **204** and the anode **216** that has a power between about 0.01 kW and 100 kW depending on the volume of the plasma. The pulse **302** is sufficient to ignite the feed gas **226** to generate the weakly-ionized plasma **232**.

In one embodiment (not shown), the pulsed power supply **202** applies a potential between the cathode **204** and the anode **216** before the feed gas **226** is delivered into the region **222**. In this embodiment, the feed gas **226** is ignited as it flows between the cathode **204** and the anode **216**. In other embodiments, the pulsed power supply **202** generates the pulse **302** between the cathode **204** and the anode **216** during or after the feed gas **226** is delivered into the region **222**.

The power generated by the pulsed power supply **202** partially ionizes the feed gas **226** that is located in the region **222** between the cathode **204** and the anode **216**. The partially ionized gas is also referred to as a weakly-ionized plasma or a pre-ionized plasma **232** (FIG. 2B). The formation of the weakly-ionized plasma **232** substantially eliminates the possibility of creating a breakdown condition when high-power pulses are applied to the weakly-ionized plasma **232** as described herein.

In one embodiment, the power is continuously applied for between about one microsecond and one hundred seconds to allow the pre-ionized plasma **232** to form and to be maintained at a sufficient plasma density. In one embodiment, the power from the pulsed power supply **202** is continuously applied after the weakly-ionized plasma **232** is ignited in order to maintain the weakly-ionized plasma **232**. The pulsed power supply **202** can be designed so as to output a continuous nominal power in order to generate and sustain the weakly-ionized plasma **232** until a high-power pulse is delivered by the pulsed power supply **202**.

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At time t_2 , the pulsed power supply **202** delivers a high-power pulse **304** across the weakly-ionized plasma **232**. In some embodiments, the high-power pulse **304** has a power that is in the range of between about 1 kW and 10 MW depending on parameters of the plasma generating apparatus **200**. The high-power pulse has a leading edge **306** having a rise time of between about 0.1 microseconds and ten seconds.

The high-power pulse **304** has a power and a pulse width that is sufficient to transform the weakly-ionized plasma **232** to a strongly-ionized plasma **238** (FIG. 2D). The strongly-ionized plasma **238** is also referred to as a high-density plasma. In one embodiment, the high-power pulse **304** is applied for a time that is in the range of between about ten microseconds and ten seconds. At time t_4 , the high-power pulse **304** is terminated.

The power supply **202** maintains the weakly-ionized plasma **232** after the delivery of the high-power pulse **304** by applying background power that, in one embodiment, is between about 0.01 kW and 100 kW. The background power can be a pulsed or continuously applied power that maintains the pre-ionization condition in the plasma, while the pulsed power supply **202** prepares to deliver another high-power pulse **308**.

At time t_5 , the pulsed power supply **202** delivers another high-power pulse **308**. The repetition rate between the high-power pulses **304**, **308** is, in one embodiment, between about 0.1 Hz and 1 kHz. The particular size, shape, width, and frequency of the high-power pulses **304**, **308** depend on various factors including process parameters, the design of the pulsed power supply **202**, the design of the plasma generating apparatus **200**, the volume of the plasma, and the pressure in the chamber. The shape and duration of the leading edge **306** and the trailing edge **310** of the high-power pulse **304** is chosen to sustain the weakly-ionized plasma **232** while controlling the rate of ionization of the strongly-ionized plasma **238**.

In one embodiment, the particular size, shape, width, and frequency of the high-power pulse **304** is chosen to control the density of the strongly-ionized plasma **238**. In one embodiment, the particular size, shape, width, and frequency of the high-power pulse **304** is chosen to control the etch rate of a substrate (not shown). In one embodiment, the particular size, shape, width, and frequency of the high-power pulse **304** is chosen to control the rate of sputtering of a sputtering target (not shown).

FIG. 4 illustrates graphical representations **320**, **322**, and **324** of the absolute value of applied voltage, current, and power, respectively, as a function of time for periodic pulses applied to the plasma in the plasma generating apparatus **200** of FIG. 2A. In one embodiment, at time t_0 (not shown), the feed gas **226** flows proximate to the cathode **204** before the pulsed power supply **202** is activated. The time required for a sufficient quantity of feed gas **226** to flow proximate to the cathode **204** depends on several factors including the flow rate of the feed gas **226** and the desired pressure in the region **222**.

In the embodiment shown in FIG. 4, the power supply **202** generates a constant power. At time t_1 , the pulsed power supply **202** generates a voltage **326** across the anode **216** and the cathode **204**. In one embodiment, the voltage **326** is approximately between 100V and 5 kV. The period between time t_0 and time t_1 (not shown) can be on the order of several microseconds up to several milliseconds. At time t_1 , the current **328** and the power **330** have constant value.

Between time t_1 and time t_2 , the voltage **326**, the current **328**, and the power **330** remain constant as the weakly-

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ionized plasma **232** (FIG. 2B) is generated. The voltage **332** at time t_2 is between about 100V and 5 kV. The current **334** at time t_2 is between about 0.1 A and 100 A. The power **336** delivered at time t_2 is between about 0.01 kW and 100 kW.

The power **336** generated by the pulsed power supply **202** partially ionizes the gas **226** that is located in the region **222** between the cathode **204** and the anode **216**. The partially ionized gas is also referred to as a weakly-ionized plasma or a pre-ionized plasma **232**. As described herein, the formation of weakly-ionized plasma **232** substantially eliminates the possibility of creating a breakdown condition when high-power pulses are applied to the weakly-ionized plasma **232**. The suppression of this breakdown condition substantially eliminates the occurrence of undesirable arcing between the anode **216** and the cathode **204**.

In one embodiment, the period between time t_1 and time t_2 is between about one microsecond and one hundred seconds to allow the pre-ionized plasma **232** to form and be maintained at a sufficient plasma density. In one embodiment, the power **336** from the pulsed power supply **202** is continuously applied to maintain the weakly-ionized plasma **232**. The pulsed power supply **202** can be designed so as to output a continuous nominal power into order to sustain the weakly-ionized plasma **232**.

Between time t_2 and time t_3 , the pulsed power supply **202** delivers a large voltage pulse **338** across the weakly-ionized plasma **232**. In some embodiments, the large voltage pulse **338** has a voltage that is in the range of 200V to 30 kV. In some embodiments, the period between time t_2 and time t_3 is between about 0.1 microseconds and ten seconds. The large voltage pulse **338** is applied between time t_3 and time t_4 , before the current across the weakly-ionized plasma **232** begins to increase. In one embodiment, the period between time t_3 and time t_4 can be between about ten nanoseconds and one microsecond.

Between time t_4 and time t_5 , the voltage **340** drops as the current **342** increases. The power **344** also increases between time t_4 and time t_5 , until a quasi-stationary state exists between the voltage **346** and the current **348**. The period between time t_4 and time t_5 can be on the order of hundreds of nanoseconds.

In one embodiment, at time t_5 , the voltage **346** is between about 50V and 30 kV thousand volts, the current **348** is between about 10 A and 5 kA and the power **350** is between about 1 kW and 10 MW. The power **350** is continuously applied to the plasma until time t_6 . In one embodiment, the period between time t_5 and time t_6 is approximately between one microsecond and ten seconds.

The pulsed power supply **202** delivers a high-power pulse having a maximum power **350** and a pulse width that is sufficient to transform the weakly-ionized plasma **232** to a strongly-ionized plasma **238** (FIG. 2D). At time t_6 , the maximum power **350** is terminated. In one embodiment, the pulsed power supply **202** continues to supply a background power that is sufficient to maintain the plasma after time t_6 .

In one embodiment, the power supply **202** maintains the plasma after the delivery of the high-power pulse by continuing to apply a power **352** that can be between about 0.01 kW and 100 kW to the plasma. The continuously generated power maintains the pre-ionization condition in the plasma, while the pulsed power supply **202** prepares to deliver the next high-power pulse.

At time t_7 , the pulsed power supply **202** delivers the next high-power pulse (not shown). In one embodiment, the repetition rate between the high-power pulses is between about 0.1 Hz and 1 kHz. The particular size, shape, width, and frequency of the high-power pulses depend on various

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factors including process parameters, the design of the pulsed power supply **202**, the design of the plasma generating system **200**, the volume of plasma, the density of the strongly-ionized plasma **238**, and the pressure in the region **222**.

In another embodiment (not shown), the power supply **202** generates a constant voltage. In this embodiment, the applied voltage **320** is continuously applied from time t_2 until time t_6 . The current **322** and the power **324** rise until time t_6 in order to maintain a constant voltage level, and then the voltage **320** is terminated. The parameters of the current, and voltage are optimized for generating excited atoms.

In one embodiment of the invention, the efficiency of the ionization process is increased by generating a magnetic field proximate to the cathode **204**. The magnetic field tends to trap electrons in the weakly-ionized plasma **232** proximate to the cathode **204**. The trapped electrons ionize the excited atoms **244** thereby generating the strongly-ionized plasma **238**. In this embodiment, magnetically enhanced plasma has strong diamagnetic properties. The term "strong diamagnetic properties" means that the magnetically enhanced high-density plasma discharge tends to exclude external magnetic fields from the plasma volume.

FIG. 5A through FIG. 5D illustrate various simulated magnetic field distributions **400**, **402**, **404**, and **406** proximate to the cathode **204** for various electron ExB drift currents in a magnetically enhanced plasma generating apparatus according to one embodiment of the invention. The magnetically enhanced plasma generating apparatus includes a magnet assembly **407** that is positioned proximate to the cathode **204**. The magnet assembly **407** generates a magnetic field proximate to the cathode **204**. In one embodiment, the strength of the magnetic field is between about fifty and two thousand gauss. The simulated magnetic fields distributions **400**, **402**, **404**, and **406** indicate that high-power plasmas having high current density tend to diffuse homogeneously in an area **23'** of the magnetically enhanced plasma generating apparatus.

The high-power pulses between the cathode **204** and the anode **216** generate secondary electrons from the cathode **204** that move in a substantially circular motion proximate to the cathode **204** according to crossed electric and magnetic fields. The substantially circular motion of the electrons generates an electron ExB drift current. The magnitude of the electron ExB drift current is proportional to the magnitude of the discharge current in the plasma and, in one embodiment, is approximately in the range of between about three and ten times the magnitude of the discharge current.

In one embodiment, the substantially circular electron ExB drift current generates a magnetic field that interacts with the magnetic field generated by the magnet assembly **407**. In one embodiment, the magnetic field generated by the electron ExB drift current has a direction that is substantially opposite to the magnetic field generated by the magnet assembly **407**. The magnitude of the magnetic field generated by the electron ExB drift current increases with increased electron ExB drift current. The homogeneous diffusion of the strongly-ionized plasma in the region **234'** is caused, at least in part, by the interaction of the magnetic field generated by the magnet assembly **407** and the magnetic field generated by the electron ExB drift current.

In one embodiment, the electron ExB drift current defines a substantially circular shape for low current density plasma. However, as the current density of the plasma increases, the substantially circular electron ExB drift current tends to have a more complex shape as the interaction of the magnetic field generated by the magnet assembly **407**, the

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electric field generated by the high-power pulse, and the magnetic field generated by the electron ExB drift current becomes more acute. For example, in one embodiment, the electron ExB drift current has a substantially cycloidal shape. The exact shape of the electron ExB drift current can be quite elaborate and depends on various factors.

For example, FIG. 5A illustrates the magnetic field lines **408** produced from the interaction of the magnetic field generated by the magnet assembly **407** and the magnetic field generated by an electron ExB drift current **410** illustrated by a substantially circularly shaped ring. The electron ExB drift current **410** is generated proximate to the cathode **204**.

In the example shown in FIG. 5A, the electron ExB drift current **410** is approximately 100 A. In one embodiment of the invention, the electron ExB drift current **410** is between approximately three and ten times as great as the discharge current. Thus, in the example shown in FIG. 5A, the discharge current is approximately between 10 A and 30 A. The magnetic field lines **408** shown in FIG. 5A indicate that the magnetic field generated by the magnet assembly **407** is substantially undisturbed by the relatively small magnetic field that is generated by the relatively small electron ExB drift current **410**.

FIG. 5B illustrates the magnetic field lines **412** produced from the interaction of the magnetic field generated by the magnet assembly **407** and the magnetic field generated by an electron ExB drift current **414**. The electron ExB drift current **414** is proximate to the cathode **204**. In the example shown in FIG. 5B, the electron ExB drift current **414** is approximately 300 A. Since the electron ExB drift current **414** is typically between about three and ten times as great as the discharge current, the discharge current in this example is approximately between 30 A and 100 A.

The magnetic field lines **412** that are generated by the magnet assembly **407** are substantially undisturbed by the relatively small magnetic field generated by the relatively small electron ExB drift current **414**. However, the magnetic field lines **416** that are closest to the electron ExB drift current **414** are somewhat distorted by the magnetic field generated by the electron ExB drift current **414**. The distortion suggests that a larger electron ExB drift current should generate a stronger magnetic field that will interact more strongly with the magnetic field generated by the magnet assembly **407**.

FIG. 5C illustrates the magnetic field lines **418** that are produced from the interaction of the magnetic field generated by the magnet assembly **407** and the magnetic field generated by an electron ExB drift current **420**. The electron ExB drift current **420** is generated proximate to the cathode **204**. In the example shown in FIG. 5C, the electron ExB drift current **420** is approximately 1,000 A. Since the electron ExB drift current **420** is typically between about three and ten times as great as the discharge current, the discharge current in this example is approximately between 100 A and 300 A.

The magnetic field lines **418** that are generated by the magnet assembly **407** exhibit substantial distortion that is caused by the relatively strong magnetic field generated by the relatively large electron ExB drift current **420**. Thus, the larger electron ExB drift current **420** generates a stronger magnetic field that strongly interacts with and can begin to dominate the magnetic field generated by the magnet assembly **407**.

The interaction of the magnetic field generated by the magnet assembly **407** and the magnetic field generated by the electron ExB drift current **420** generates magnetic field

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lines **422** that are somewhat more parallel to the surface of the cathode **204** than the magnetic field lines **408**, **412**, and **416** in FIG. 5A and FIG. 5B. The magnetic field lines **422** allow the strongly-ionized plasma **238** to more uniformly distribute itself in the area **234**. Thus, the strongly-ionized plasma **238** is substantially uniformly diffused in the area **234**.

FIG. 5D illustrates the magnetic field lines **424** produced from the interaction of the magnetic field generated by the magnet assembly **407** and the magnetic field generated by an electron ExB drift current **426**. The electron ExB drift current **426** is generated proximate to the cathode **204**. In the example shown in FIG. 5D, the electron ExB drift current **426** is approximately 5 kA. The discharge current in this example is approximately between 500 A and 1,700 A.

The magnetic field lines **424** generated by the magnet assembly **407** are relatively distorted due to their interaction with the relatively strong magnetic field generated by the relatively large electron ExB drift current **426**. Thus, in this embodiment, the relatively large electron ExB drift current **426** generates a very strong magnetic field that is stronger than the magnetic field generated by the magnet assembly **407**.

FIG. 6A through FIG. 6D illustrate cross-sectional views of alternative embodiments of plasma generating systems **200'**, **200''**, **200'''** and **200''''**, according to the present invention. The plasma generating system **200'** of FIG. 6A includes an electrode **452** that generates a weakly-ionized or pre-ionized plasma. The electrode **452** is also referred to as a pre-ionizing filament electrode and is a component in an ionization source that generates the weakly-ionized plasma.

In one embodiment, the electrode **452** is coupled to an output **454** of a power supply **456**. The power supply **456** can be a DC power supply or an AC power supply. An insulator **458** isolates the electrode **452** from the anode **216**. In one embodiment, the electrode **452** is substantially shaped in the form of a ring electrode. In other embodiments, the electrode **452** is substantially shaped in a linear form or any other shape that is suitable for pre-ionizing the plasma.

In one embodiment, a second output **460** of the power supply **456** is coupled to the cathode **204**. The insulator **218** isolates the cathode **204** from the anode **216**. In one embodiment, the power supply **456** generates an average output power that is in the range of between about 0.01 kW and 100 kW. Such an output power is sufficient to generate a suitable current between the electrode **452** and the cathode **204** to pre-ionize feed gas **226** that is located proximate to the electrode **452**.

In operation, the plasma generating apparatus **200'** functions in a similar manner to the plasma generating apparatus **200** of FIG. 2A, but with some operational differences. In one embodiment (not shown) a magnetic field is generated proximate to the cathode **204**. In one embodiment, the strength of the magnetic field is between about fifty and two thousand gauss. The feed gas **226** is supplied proximate to the electrode **452** and the cathode **204**.

201 The power supply **456** applies a suitable current between the cathode **204** and the electrode **452**. The parameters of the current are chosen to establish a weakly-ionized plasma in the region **234** proximate to the electrode **452**. In one embodiment, the power supply **456** generates a voltage of between about 100V and 5 kV with a discharge current that is between about 0.1 A and 100 A depending on the size of the system. An example of specific parameters of the voltage will be discussed herein in more detail in connection with FIG. 7.

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In one embodiment, the resulting pre-ionized plasma density is in the range between approximately 10^6 and 10^{12} cm⁻³ for argon sputtering gas. In one embodiment, the pressure in the region 234 is in the range of approximately 10^{-3} to 10 Torr or higher. The pressure can vary depending on various system parameters, such as the presence of a magnetic field proximate to the cathode 204. As previously discussed, the weakly-ionized or pre-ionized plasma substantially eliminates the possibility of establishing a breakdown condition between the cathode 204 and the anode 216 when high-power pulses are applied to the plasma.

The pulsed power supply 202 then generates a high-power pulse between the cathode 204 and the anode 216. The high-power pulse generates a strongly-ionized plasma from the weakly-ionized plasma. The parameters of the high-power pulse depend on various parameters including the volume of the plasma, the desired plasma density, and the pressure in the region 234.

In one embodiment, the high-power pulse between the cathode 204 and the anode 216 is in the range of about 1 kW to about 10 MW. In one embodiment, the discharge current density that can be generated from the strongly-ionized plasma is greater than about 1 A/cm² for a pressure of approximately 10 mTorr.

In one embodiment, the high-power pulse has a pulse width that is in the range of approximately one microsecond to several seconds. In one embodiment, the repetition rate of the high-power discharge is in the range of between about 0.1 Hz to 10 kHz. In one embodiment, the average power generated by the pulsed power supply is less than 1 MW depending on the size of the system. In one embodiment, the thermal energy in the cathode 204 and/or the anode 216 can be conducted away or dissipated by liquid or gas cooling (not shown).

In one embodiment (not shown), a magnetic field is generated proximate to the cathode 204. The strongly-ionized plasma tends to diffuse homogeneously in the area 234 due to the interaction of generated magnetic fields, as described herein in connection with FIG. 5A through FIG. 5D.

FIG. 6B is a cross-sectional view of another embodiment of a plasma generating apparatus 200" according to the present invention. This embodiment is similar to the plasma generating apparatus 200' of FIG. 6A. However, in this embodiment, the electrode 452', which is a component of the ionization source, substantially surrounds the cathode 204. The position of the electrode 452' relative to the cathode 204 is chosen to achieve particular electrical conditions in the gap 220 between the anode 216 and the cathode 204.

For example, a distance 462 between the electrode 452' and the cathode 204 can be varied by changing the diameter of the electrode 452'. In one embodiment, the distance 462 can be varied from about 0.1 cm to about 10 cm. The distance 462 can be optimized to generate a sustainable weakly-ionized plasma in the region 234. The vertical position of the electrode 452' relative to the cathode 204 can also be varied.

The pre-ionizing electrode 452' is not physically located in the region 222 between the anode 216 and the cathode 204. Therefore, the pre-ionizing electrode 452' does not interfere with the strong electric field that results when a high-power pulse from the pulsed power supply 202 is applied between the anode 216 and the cathode 204. Additionally, the location of the pre-ionizing electrode 452' results in a more uniformly distributed weakly-ionized plasma in the region 234.

In operation, the power supply 456 applies a voltage between the cathode 204 and the electrode 452'. The voltage

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generates a weakly-ionized or pre-ionized plasma proximate to the electrode 452' and the cathode 204. The pre-ionized plasma substantially eliminates the possibility of establishing a breakdown condition when high-power pulses from the pulsed power supply 202 are applied to the plasma.

In one embodiment, the power supply 456 is a DC power supply that generates a DC voltage that is in the range of between about 100V and 5 kV with a discharge current that is in the range of between about 0.1 A and 100 A. In another embodiment, the power supply 456 is an AC power supply that generates voltage pulses between the cathode 204 and the electrode 452'.

FIG. 6C is a cross-sectional view of another embodiment of a plasma generating apparatus 200''' according to the present invention. The configuration of the electrode 452 and the cathode 204' can affect the parameters of the electric field generated between the electrode 452 and the cathode 204'. The parameters of the electric field can influence the ignition of the pre-ionized plasma as well as the pre-ionization process generally. This embodiment creates the necessary conditions for breakdown of the feed gas and ignition of the weakly-ionized plasma in the region 222 between the anode 216 and the cathode 204'.

In the embodiment illustrated by FIG. 6C, the electric field lines (not shown) generated between the cathode 204' and the electrode 452 are substantially perpendicular to the cathode 204' at the point 470 on the cathode 204'. The electric field in the gap 472 between the electrode 452 and the cathode 204' is adapted to ignite the plasma from the feed gas 226 flowing through the gap 472. The efficiency of the pre-ionization process can be increased using this embodiment depending upon parameters, such as the magnetic field strength and the pressure in the area proximate to the cathode 204'.

FIG. 6D is a cross-sectional view of another embodiment of a plasma generating apparatus 200'''' according to the present invention. In this embodiment, the electric field lines (not shown) generated between the cathode 204'' and the electrode 452 are substantially perpendicular to the cathode 204'' at the point 474. The electric field in the gap 476 between the electrode 452 and the cathode 204'' is adapted to ignite the plasma from the feed gas 226 flowing through the gap 476. The efficiency of the pre-ionization process can be increased using this embodiment depending upon parameters, such as the magnetic field strength and the pressure in the area proximate to the cathode 204''.

FIG. 7 illustrates a graphical representation 500 of the pulse power as a function of time for periodic pulses applied to the plasma in the plasma generating system 200' of FIG. 6A. In one embodiment, the feed gas 226 flows in the region 222 proximate to the electrode 452 at time t_0 , before either the power supply 456 or the pulsed power supply 202 are activated.

In another embodiment, the power supply 456 and/or the pulsed power supply 202 are activated at time t_0 before the gas 226 flows in the region 222 proximate to the electrode 452. In this embodiment, the feed gas 226 is injected between the electrode 452 and the cathode 204 where it is ignited by the power supply 456 to generate the weakly-ionized plasma.

The time required for a sufficient quantity of gas 226 to flow into the region 222 depends on several factors including the flow rate of the gas 226 and the desired operating pressure. At time t_1 , the power supply 456 generates a power 502 that is in the range of between about 0.01 kW to about 100 kW between the electrode 452 and the cathode 204. The power 502 causes the gas 226 proximate to the electrode 452

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to become partially ionized, thereby generating a weakly-ionized plasma or a pre-ionized plasma.

At time t_2 , the pulsed power supply **202** delivers a high-power pulse **504** to the weakly-ionized plasma that is on the order of less than 1 kW to about 10 MW depending on the volume of the plasma and the operating pressure. The high-power pulse **504** is sufficient to transform the weakly-ionized plasma to a strongly-ionized plasma. The high-power pulse has a leading edge **506** having a rise time that is between about 0.1 microseconds and ten seconds.

In one embodiment, the pulse width of the high-power pulse **504** is in the range of between about one microsecond and ten seconds. The high-power pulse **504** is terminated at time t_4 . Even after the delivery of the high-power pulse **504**, the power **502** from the power supply **456** is continuously applied to sustain the pre-ionized plasma, while the pulsed power supply **202** prepares to deliver another high-power pulse **508**. In another embodiment (not shown), the power supply **456** is an AC power supply and delivers suitable power pulses to ignite and sustain the weakly-ionized plasma.

At time t_5 , the pulsed power supply **202** delivers another high-power pulse **508**. In one embodiment, the repetition rate of the high-power pulses can be between about 0.1 Hz and 10 kHz. The particular size, shape, width, and frequency of the high-power pulse depend on the process parameters, such as the operating pressure, the design of the pulsed power supply **202**, the presence of a magnetic field proximate to the cathode **204**, and the volume of the plasma. The shape and duration of the leading edge **506** and the trailing edge **510** of the high-power pulse **504** is chosen to control the rate of ionization of the strongly-ionized plasma.

FIG. **8** is a flowchart **600** of an illustrative process of generating a high-density or strongly-ionized plasma according to the present invention. The process is initiated (step **602**) by activating various systems in the plasma generating apparatus **200** of FIG. **2A**. For example, a chamber (not shown) is initially pumped down to a specific pressure (step **604**). Next, the pressure in the chamber is evaluated (step **606**). In one embodiment, feed gas **226** is then pumped into the chamber (step **608**). The gas pressure is evaluated (step **610**). If the gas pressure is correct, the pressure in the chamber is again evaluated (step **612**).

An appropriate magnetic field is generated proximate to the feed gas **226** (not shown) when the pressure in the chamber is correct. In one embodiment, a magnet assembly (not shown) can include at least one permanent magnet, and thus the magnetic field is generated constantly, even before the process is initiated. In another embodiment, a magnetic assembly (not shown) includes at least one electromagnet, and thus the magnetic field is generated only when the electromagnet is operating.

The feed gas **226** is ionized to generate a weakly-ionized plasma **232** (step **614**). In one embodiment, the weakly-ionized plasma **232** can be generated by creating a relatively low current discharge in the gap **220** between the cathode **204** and the anode **216** of FIG. **2A**. In another embodiment the weakly-ionized plasma **232** can be generated by creating a relatively low current discharge between the electrode **452** and the cathode **204** of FIG. **6A**. In yet another embodiment (not shown), an electrode is heated to emit electrons proximate to the cathode **204**. In this embodiment, a relatively low current discharge is created between the anode **216** and the electrode in order to generate the weakly-ionized plasma **232**.

In the embodiment shown in FIG. **2A**, the weakly-ionized plasma **232** is generated by applying a potential across the

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gap **220** between the cathode **204** and the anode **216** before the introduction of the feed gas **226**. In the embodiment shown in FIG. **6A**, the weakly-ionized plasma **232** is generated by applying a potential difference between the electrode **452** and the cathode **204** before the introduction of the feed gas **226** to generate the weakly-ionized plasma **232**.

After the gas is weakly-ionized (step **616**), a strongly-ionized plasma **238** (FIG. **2D**) is generated from the weakly-ionized plasma **232** (step **618**). In one embodiment, the strongly-ionized plasma **238** is generated by applying a high-power pulse between the cathode **204** and the anode **216**. The high-power pulse results in a strong electric field **236** being generated in the gap **220** between the anode **216** and the cathode **204** as described herein. The strong electric field **236** results in a stepwise ionization process of the feed gas **226**. In one embodiment, molecular gases are used for the feed gas **226**. In this embodiment, the strong electric field **236** increases the formation of ions, which enhances the strongly-ionized plasma **238**. In one embodiment, the strongly-ionized plasma **238** is substantially homogeneous in the area **234** of FIG. **2D**.

After the strongly-ionized plasma **238** is formed (step **620**), it is maintained as required by the plasma process (step **622**). Once the plasma process is completed (step **624**), the plasma process is ended (step **626**).

Equivalents

While the invention has been particularly shown and described with reference to specific preferred embodiments, it should be understood by those skilled in the art that various changes in form and detail may be made therein without departing from the spirit and scope of the invention as defined herein.

What is claimed is:

1. An apparatus for generating a strongly-ionized plasma in a chamber, the apparatus comprising:
 - a) an ionization source that generates a weakly-ionized plasma from a feed gas, the weakly-ionized plasma reducing the probability of developing an electrical breakdown condition in the chamber;
 - a) a power supply that supplies power to the weakly-ionized plasma though an electrical pulse applied across the weakly-ionized plasma, the electrical pulse having a magnitude and a rise-time that is sufficient to increase the density of the weakly-ionized plasma to generate a strongly-ionized plasma; and
 - a) a gas line that supplies feed gas to the strongly-ionized plasma, the feed gas diffusing the strongly-ionized plasma, thereby allowing additional power from the pulsed power supply to be absorbed by the strongly-ionized plasma.
2. The apparatus of claim 1 wherein the power supply applies the electrical pulse across the weakly-ionized plasma to excite atoms in the weakly-ionized plasma and to generate secondary electrons, the secondary electrons ionizing the excited atoms, thereby creating the strongly-ionized plasma.
3. The apparatus of claim 1 wherein the gas line supplies additional feed gas that exchanges the weakly-ionized plasma while applying the electrical pulse across.
4. The apparatus of claim 1 wherein the power supply generates a constant power.
5. The apparatus of claim 1 wherein the power supply generates a constant voltage.
6. The apparatus of claim 1 wherein the ionization source is chosen from the group comprising an electrode coupled to a DC power supply, an electrode coupled to an AC power

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supply, a UV source, an X-ray source, an electron beam source, an ion beam source, an inductively coupled plasma source, a capacitively coupled plasma source, and a microwave plasma source.

7. The apparatus of claim 1 further comprising a magnet that is positioned to generate a magnetic field proximate to the weakly-ionized plasma, the magnetic field trapping electrons in the weakly-ionized plasma.

8. The apparatus of claim 7 wherein the magnet comprises an electro-magnet.

9. The apparatus of claim 7 wherein the magnet is movable.

10. A method for generating a strongly-ionized plasma in a chamber, the method comprising:

ionizing a feed gas to form a weakly-ionized plasma that reduces the probability of developing an electrical breakdown condition in the chamber;

supplying power to the weakly-ionized plasma by applying an electrical pulse across the weakly-ionized plasma, the electrical pulse having a magnitude and a rise-time that is sufficient to increase the density of the weakly-ionized plasma to generate a strongly-ionized plasma; and

diffusing the strongly-ionized plasma with additional feed gas thereby allowing the strongly-ionized plasma to absorb additional energy from the power supply.

11. The method of claim 10 wherein the applying the electrical pulse across the weakly-ionized plasma excites atoms in the weakly-ionized plasma and generates secondary electrons, the secondary electrons ionizing the excited atoms, thereby creating a strongly-ionized plasma.

12. The method of claim 10 further comprising exchanging the weakly-ionized plasma with additional feed gas.

13. The method of claim 10 wherein the applying the electrical pulse comprises applying a quasi-static electric field across the weakly-ionized plasma.

14. The method of claim 10 further comprising selecting at least one of a pulse amplitude and a pulse width of the electrical pulse in order to increase an ionization rate of the strongly-ionized plasma.

15. The method of claim 10 further comprising selecting at least one of a pulse amplitude and a pulse width of the electrical pulse in order to cause the strongly-ionized plasma to be substantially uniform.

16. The method of claim 10 wherein the electrical pulse comprises a rise time that is less than about 100V/ μ sec.

17. The method of claim 10 wherein the peak plasma density of the weakly-ionized plasma is less than about 10^{12} cm⁻³.

18. The method of claim 10 wherein the peak plasma density of the strongly-ionized plasma is greater than about 10^{12} cm⁻³.

19. The method of claim 10 wherein the ionizing the feed gas comprises exposing the feed gas to one of a static electric field, an pulsed electric field, UV radiation, X-ray radiation, electron beam radiation, and an ion beam.

20. The method of claim 10 further comprising generating a magnetic field proximate to the weakly-ionized plasma, the magnetic field trapping electrons in the weakly-ionized plasma.

21. An apparatus for generating a strongly-ionized plasma, the apparatus comprising:

an anode;

a cathode that is positioned adjacent to the anode and forming a gap there between;

an ionization source that generates a weakly-ionized plasma proximate to the cathode, the weakly-ionized

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plasma reducing the probability of developing an electrical breakdown condition between the anode and the cathode; and

a power supply that produces an electric field across the gap, the electric field generating excited atoms in the weakly-ionized plasma and generating secondary electrons from the cathode, the secondary electrons ionizing the excited atoms, thereby creating the strongly-ionized plasma.

22. The apparatus of claim 21 wherein the power supply generates a constant power.

23. The apparatus of claim 21 wherein the power supply generates a constant voltage.

24. The apparatus of claim 21 wherein the electric field comprises a quasi-static electric field.

25. The apparatus of claim 21 wherein the electric field comprises a pulsed electric field.

26. The apparatus of claim 21 wherein a rise time of the electric field is chosen to increase an ionization rate of the excited atoms in the weakly-ionized plasma.

27. The apparatus of claim 21 wherein the strongly-ionized plasma is substantially uniform proximate to the cathode.

28. The apparatus of claim 21 wherein a dimension of the gap between the anode and the cathode is chosen to increase an ionization rate of the excited atoms in the weakly-ionized plasma.

29. The apparatus of claim 21 wherein the ionization source is chosen from the group comprising an electrode coupled to a DC power supply, an electrode coupled to an AC power supply, a UV source, an X-ray source, an electron beam source, an ion beam source, an inductively coupled plasma source, a capacitively coupled plasma source, and a microwave plasma source.

30. The apparatus of claim 21 further comprising a magnet that is positioned to generate a magnetic field proximate to the weakly-ionized plasma, the magnetic field trapping electrons in the weakly-ionized plasma proximate to the cathode.

31. A method for generating a strongly-ionized plasma, the method comprising:

ionizing a feed gas to generate a weakly-ionized plasma proximate to a cathode, the weakly-ionized plasma reducing the probability of developing an electrical breakdown condition proximate to the cathode; and

applying an electric field across the weakly-ionized plasma in order to excite atoms in the weakly-ionized plasma and to generate secondary electrons from the cathode, the secondary electrons ionizing the excited atoms, thereby creating the strongly-ionized plasma.

32. The method of claim 31 wherein the applying the electric field comprises applying a quasi-static electric field.

33. The method of claim 31 wherein the applying an electric field comprises applying the electric field at a constant power.

34. The method of claim 31 wherein the applying an electric field comprises applying the electric field at a constant voltage.

35. The method of claim 31 wherein the applying the electric field comprises applying an electrical pulse across the weakly-ionized plasma.

36. The method of claim 35 further comprising selecting at least one of a pulse amplitude and a pulse width of the electrical pulse in order to increase an ionization rate of the strongly-ionized plasma.

37. The method of claim 35 further comprising selecting at least one of a pulse amplitude and a pulse width of the

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electrical pulse in order to cause the strongly-ionized plasma to be substantially uniform in an area adjacent to a surface of the cathode.

38. The method of claim 31 wherein the strongly-ionized plasma is substantially uniform proximate to the cathode.

39. The method of claim 31 further comprising generating a magnetic field proximate to the weakly-ionized plasma, the magnetic field trapping electrons in the weakly-ionized plasma.

40. An apparatus for generating a strongly-ionized plasma in a chamber, the apparatus comprising:

means for ionizing a feed gas to form a weakly-ionized plasma that reduces the probability of developing an electrical breakdown condition in the chamber;

means for supplying power to the weakly-ionized plasma by applying an electrical pulse across the weakly-ionized plasma, the electrical pulse having a magnitude and a rise-time that is sufficient to increase the density of the weakly-ionized plasma to generate a strongly-ionized plasma; and

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means for diffusing the strongly-ionized plasma with additional feed gas to allow additional power to be absorbed by the strongly-ionized plasma.

41. An apparatus for generating a strongly-ionized plasma, the apparatus comprising:

means for ionizing a feed gas to generate a weakly-ionized plasma proximate to a cathode, the weakly-ionized plasma reducing the probability of developing an electrical breakdown condition proximate to the cathode; and

means for applying an electric field across the weakly-ionized plasma in order to excite atoms in the weakly-ionized plasma and to generate secondary electrons from the cathode, the secondary electrons ionizing the excited atoms, thereby creating the strongly-ionized plasma.

42. The apparatus of claim 1 wherein the power supply comprises the ionization source.

43. The apparatus of claim 21 wherein the power supply comprises the ionization source.

* * * * *

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,853,142 B2
DATED : February 8, 2005
INVENTOR(S) : Roman Chistyakov

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 24,

Line 3, replace "plasme" with -- plasma --

Signed and Sealed this

Twenty-fourth Day of May, 2005

A handwritten signature in black ink on a light gray dotted background. The signature reads "Jon W. Dudas" in a cursive, stylized script. The "J" is large and loops around the "on". The "W" is written with two distinct peaks. The "D" is large and loops around the "udas".

JON W. DUDAS

Director of the United States Patent and Trademark Office